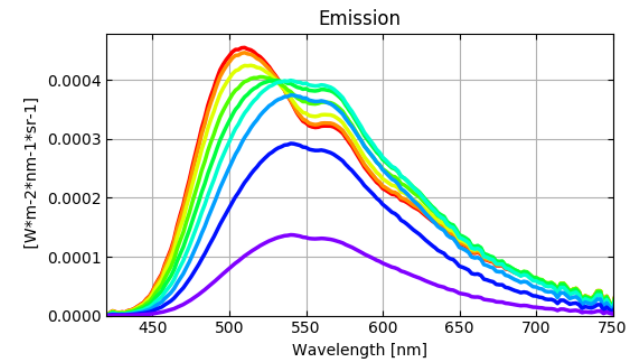
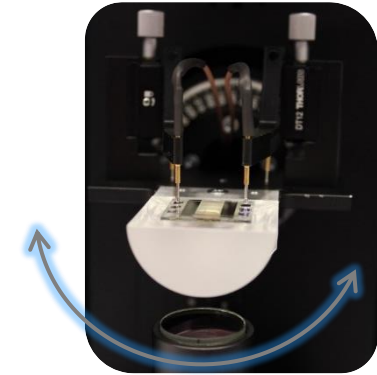
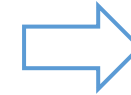
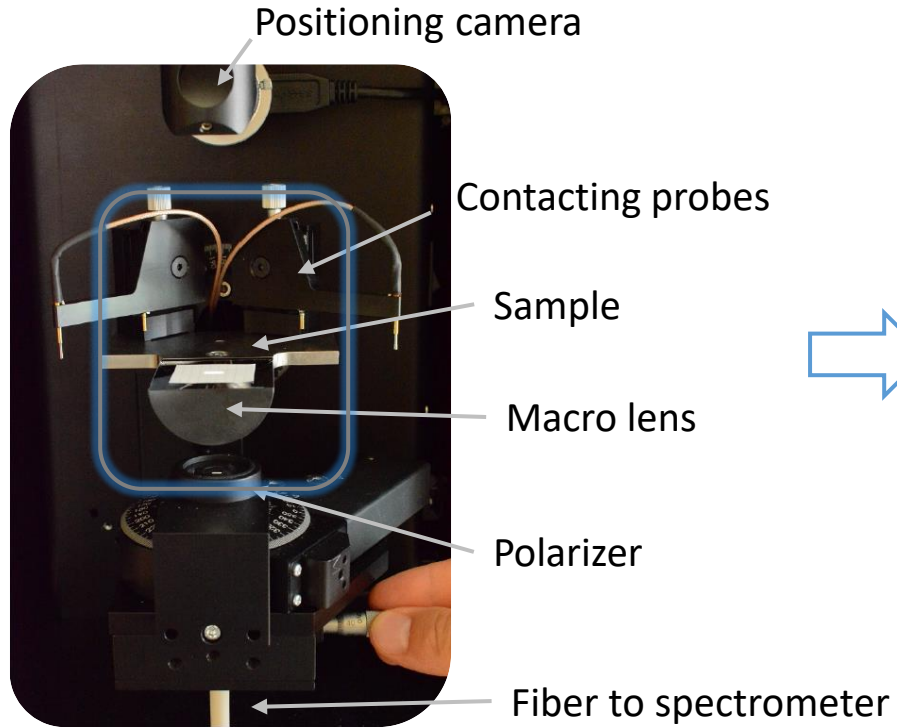
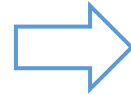


Phelos

angular luminescence spectrometer



Phelos inside



Electrical (SMU):

- Voltage: +/- 20 V
- Current: +/- 120 mA
- Resolution: < 1nA
- Source current or voltage

Angular:

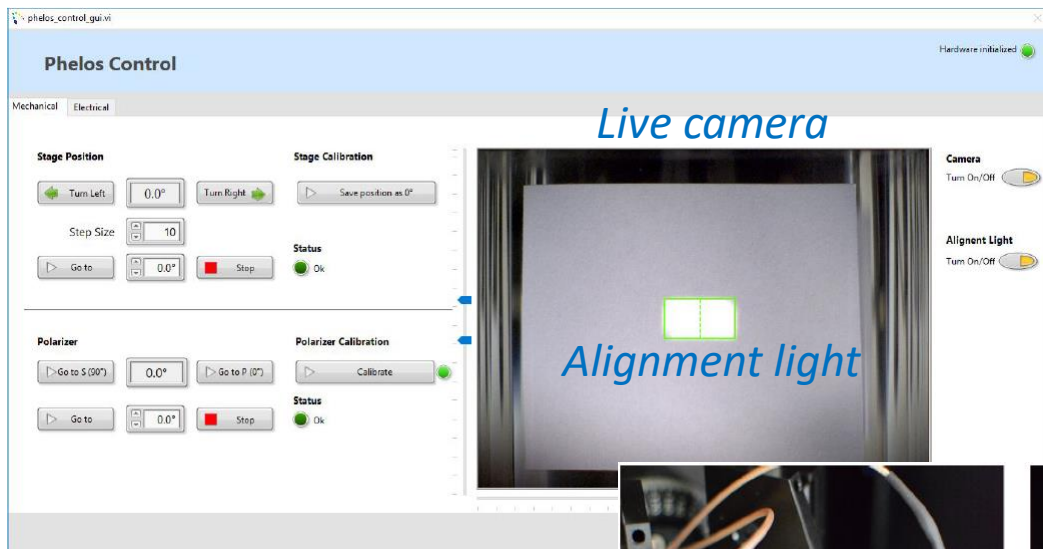
- Resolution: < 1°
- Range: +/- 85°
- Rotation: inclination angle

Spectral:

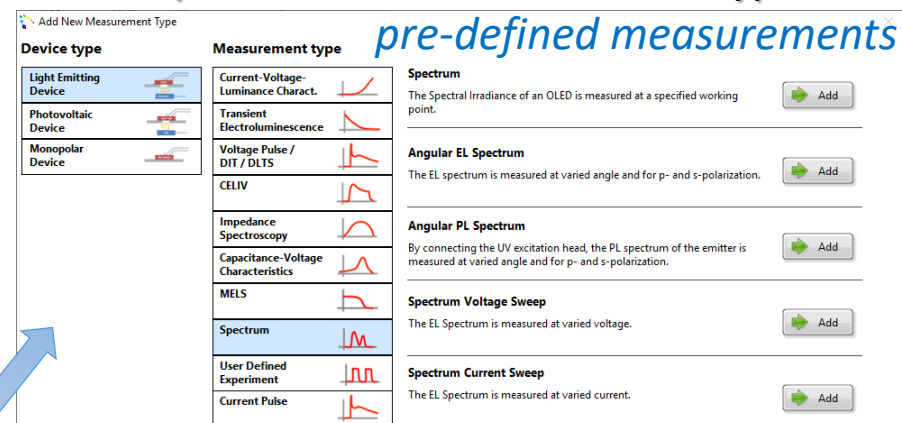
- range: 380 – 880/1100 nm
- resolution: 1.2/2.4 nm

User-friendly software

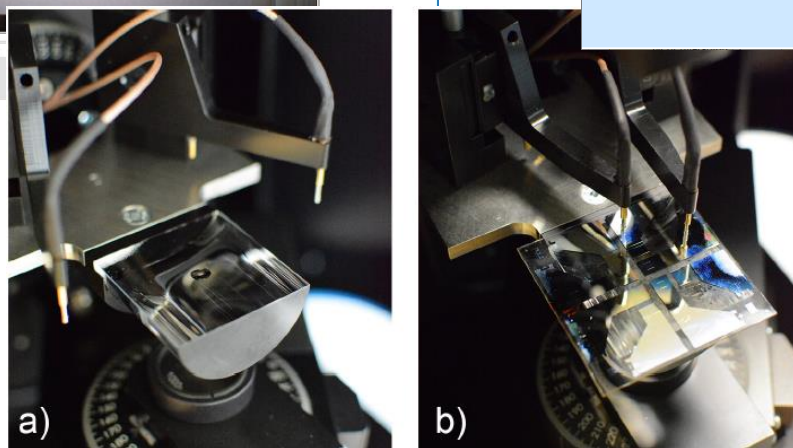
1) Mark measurement spot



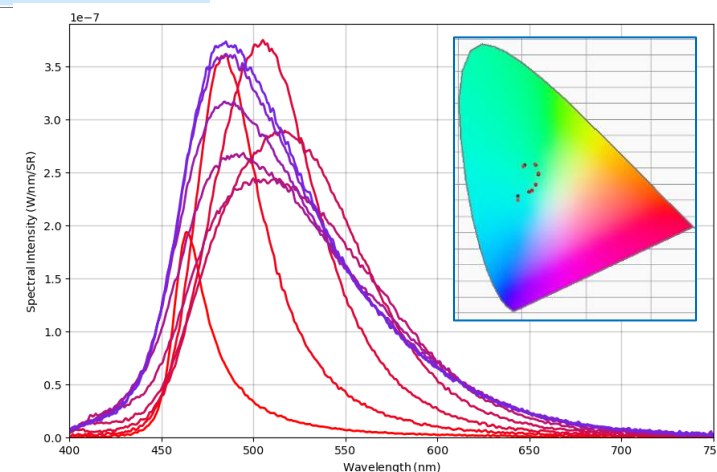
3) Choose the measurement type



4) Get high quality data

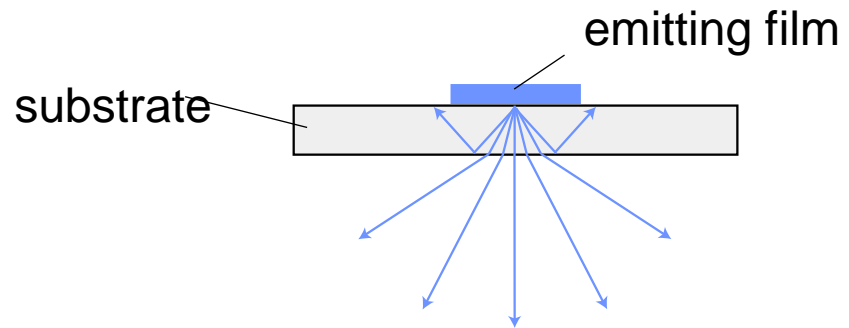


2) Place your sample



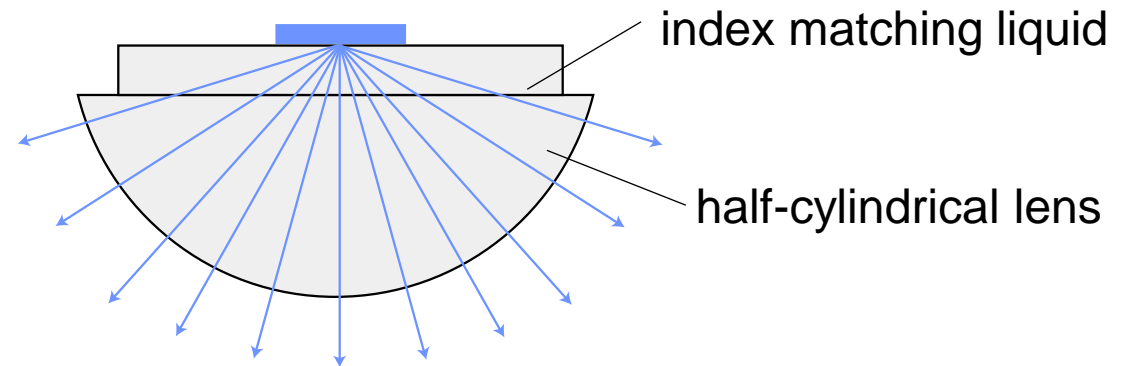
Why using a lens?

Light extraction: **bare sample**



→ total internal reflection at $\sim 42^\circ$

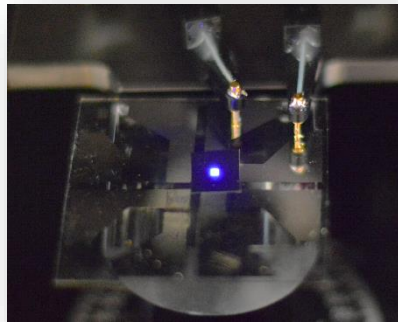
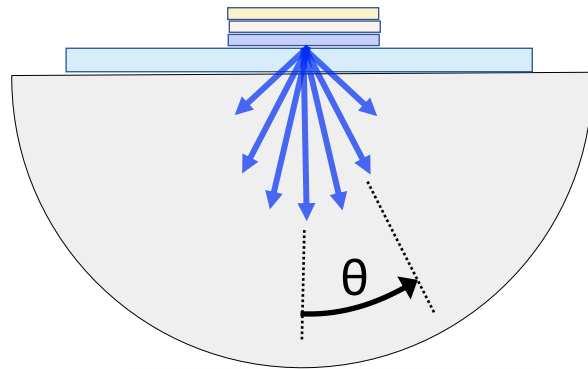
with **macro extractor lens**



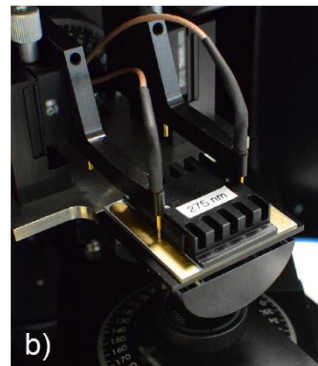
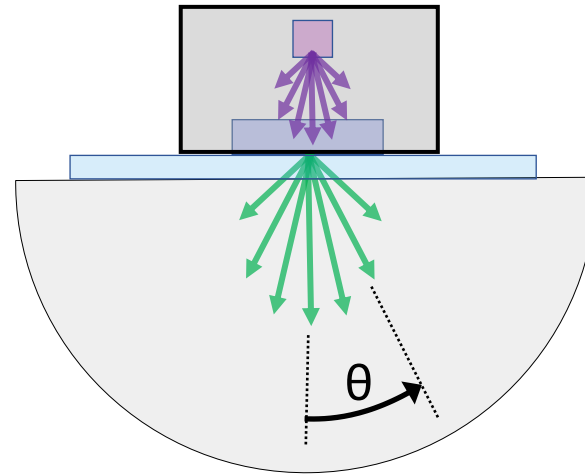
→ Outcoupling of substrate modes

Phelos modes

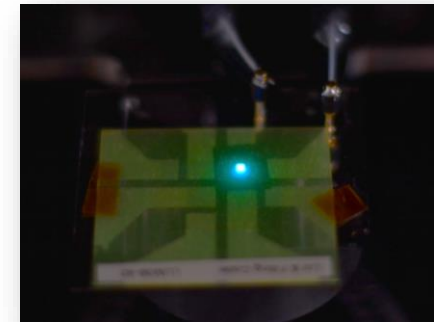
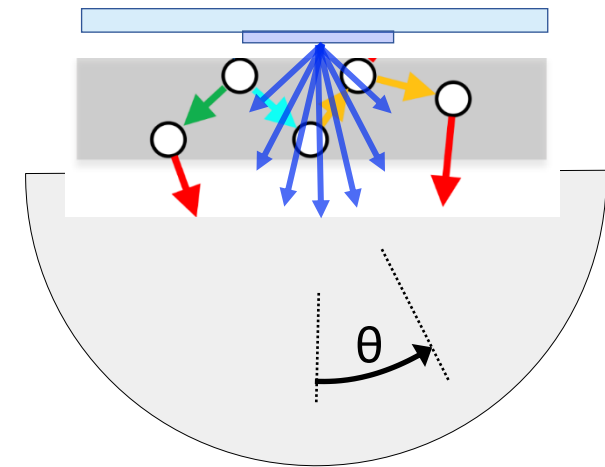
1) (O)LED
(Electroluminescence)



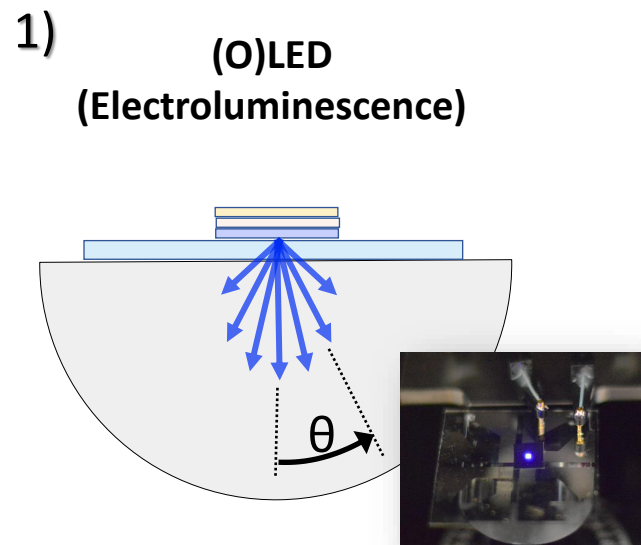
2) Emitter film
(Photoluminescence)



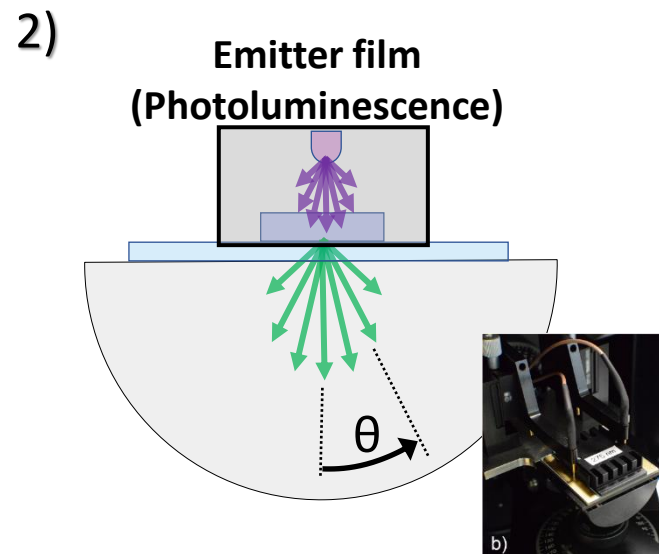
3) QD/scattering film



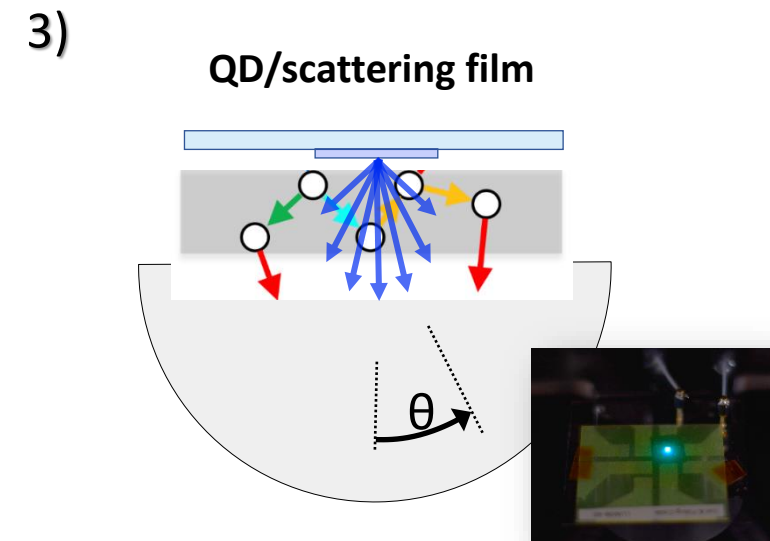
Phelos modes



- Analysis of color
- Efficiency (EQE, lm/W, power eff.)
- Emission zone fit
- Emitter orientation

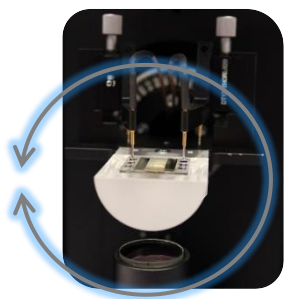


- Emitter orientation

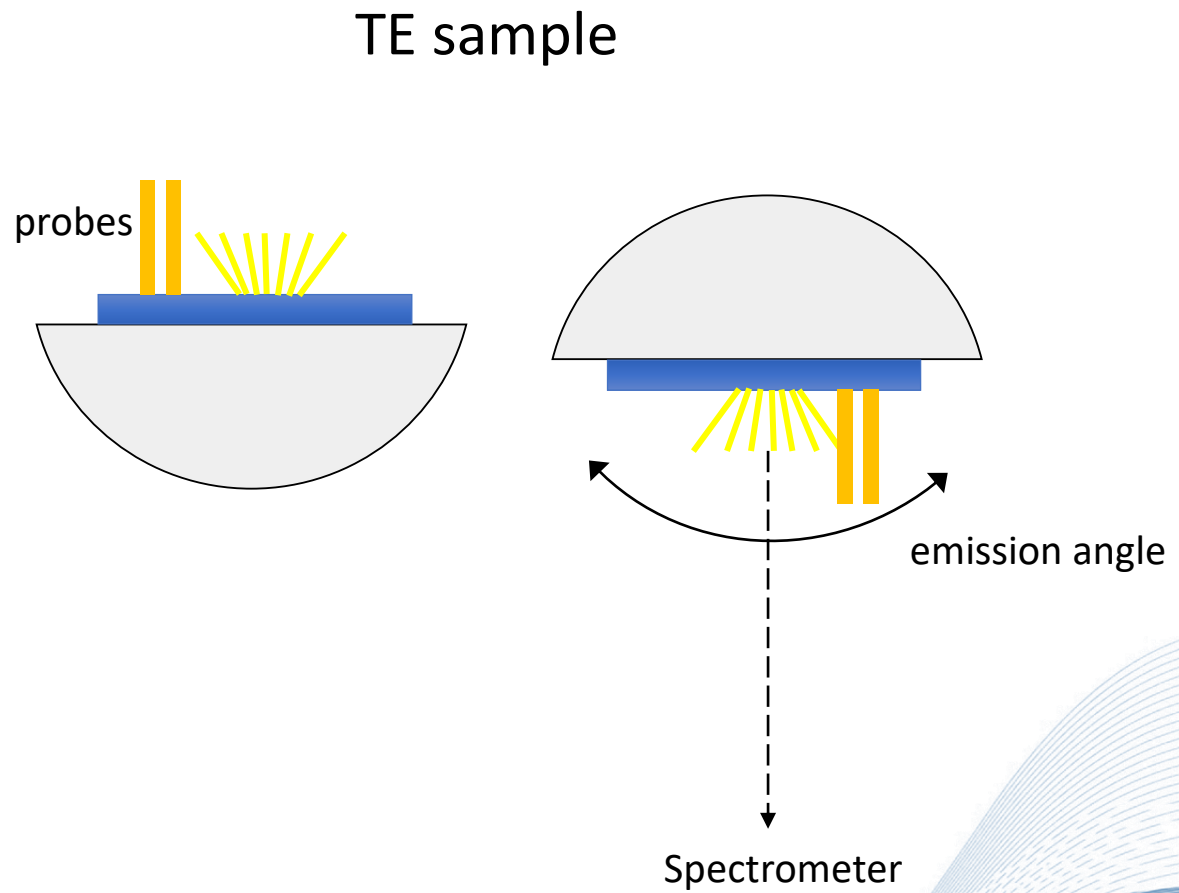
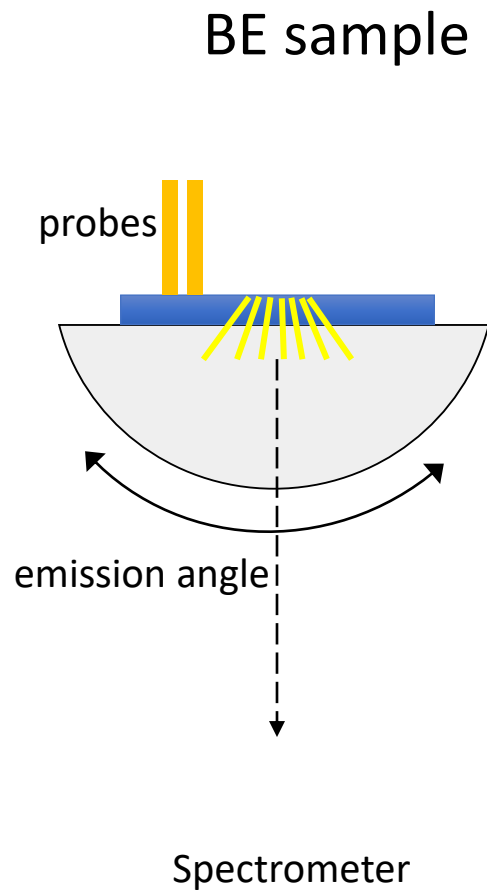


- Scattering/down-conversion film characterization
- OLED with QD characterization

Measuring BE and TE OLEDs



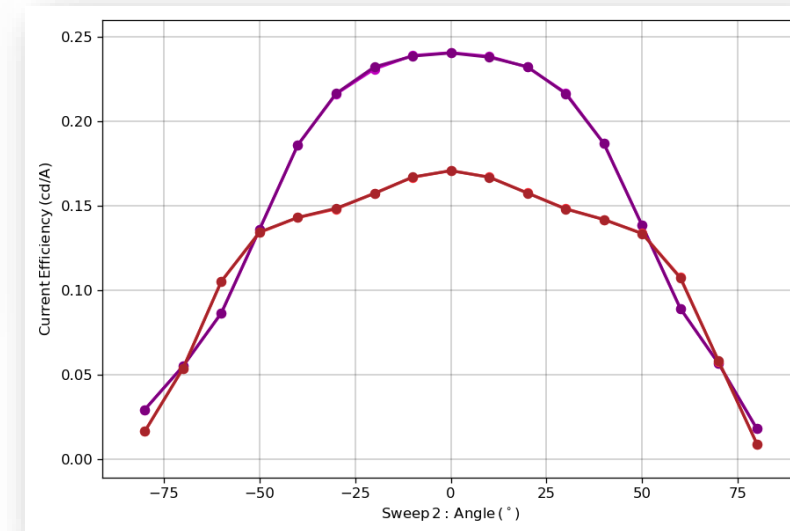
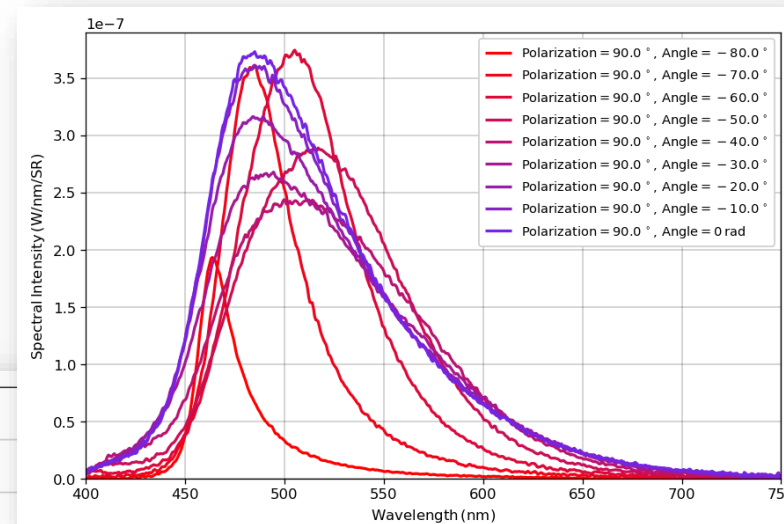
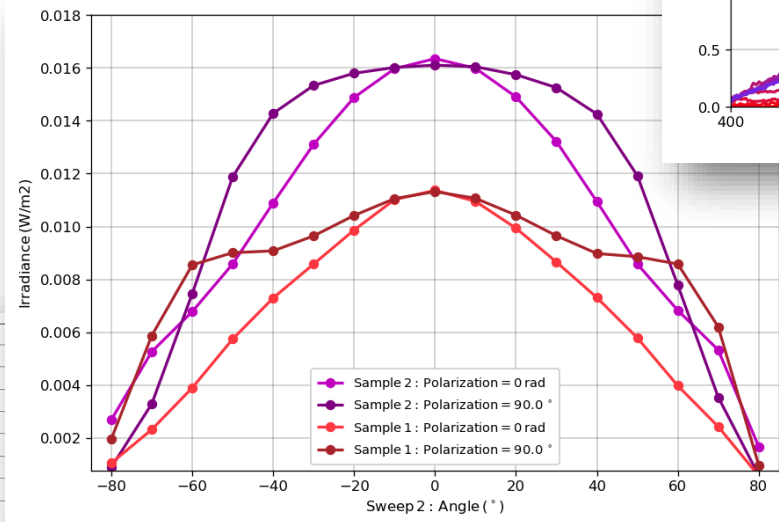
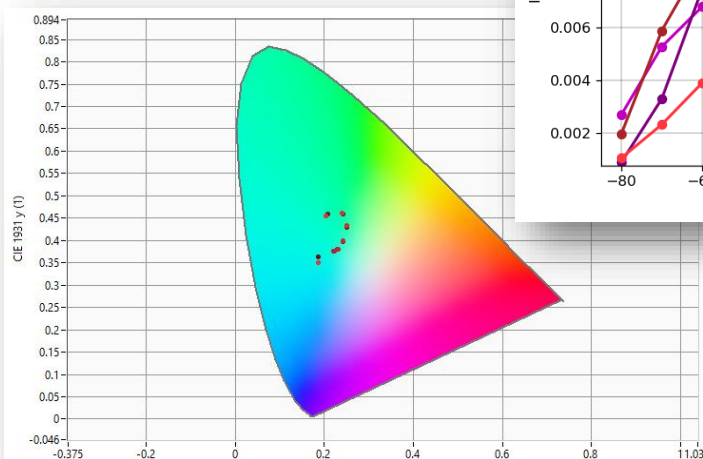
360° rotation
is possible



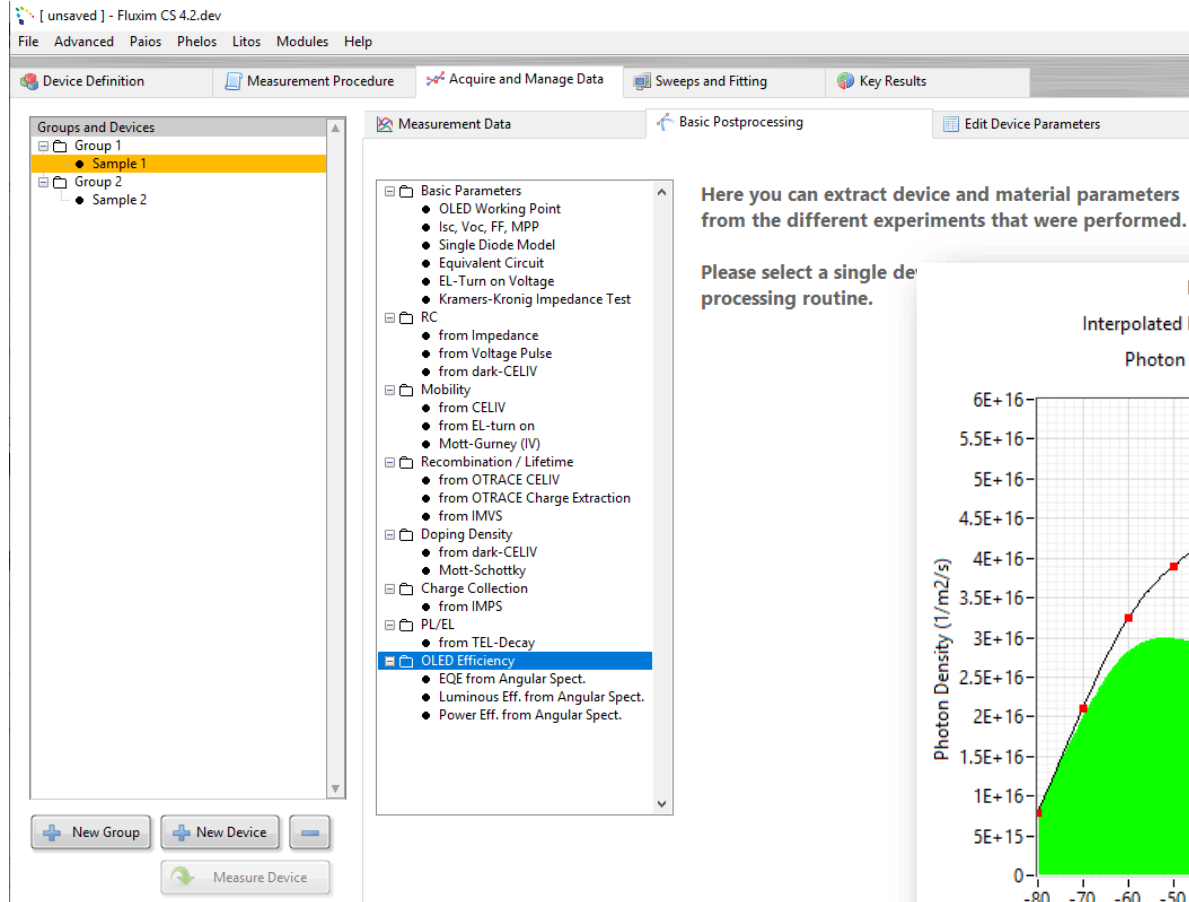
OLED example

Directly processed data:

- Spectral Irradiance/Intensity
- Radiance/Radiant Intensity
- Luminous Intensity
- Working point
- Efficacy (cd/A)
- CIE coordinates
- Color temperature, CRI
- ...



OLED efficiency post-processing



[unsaved] - Fluxim CS 4.2.dev
File Advanced Paos Phelos Litos Modules Help

Device Definition Measurement Procedure Acquire and Manage Data Sweeps and Fitting Key Results

Groups and Devices
Group 1
Sample 1
Group 2
Sample 2

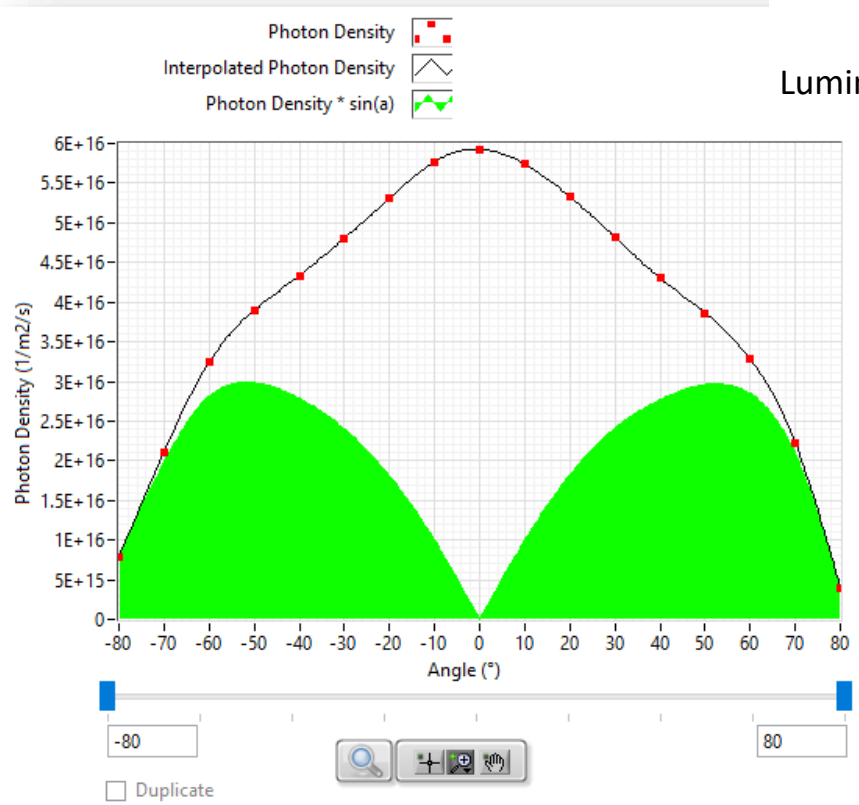
Measurement Data Basic Postprocessing Edit Device Parameters

- Basic Parameters
 - OLED Working Point
 - Isc, Voc, FF, MPP
 - Single Diode Model
 - Equivalent Circuit
 - EL-Turn on Voltage
 - Kramers-Kronig Impedance Test
- RC
 - from Impedance
 - from Voltage Pulse
 - from dark-CELIV
- Mobility
 - from CELIV
 - from EL-turn on
 - Mott-Gurney (IV)
- Recombination / Lifetime
 - from OTRACE CELIV
 - from OTRACE Charge Extraction
 - from IMVS
- Doping Density
 - from dark-CELIV
 - Mott-Schottky
- Charge Collection
 - from IMPS
- PL/EL
 - from TEL-Decay
- OLED Efficiency**
 - EQE from Angular Spect.
 - Luminous Eff. from Angular Spect.
 - Power Eff. from Angular Spect.

New Group New Device Measure Device

Here you can extract device and material parameters from the different experiments that were performed.

Please select a single de processing routine.

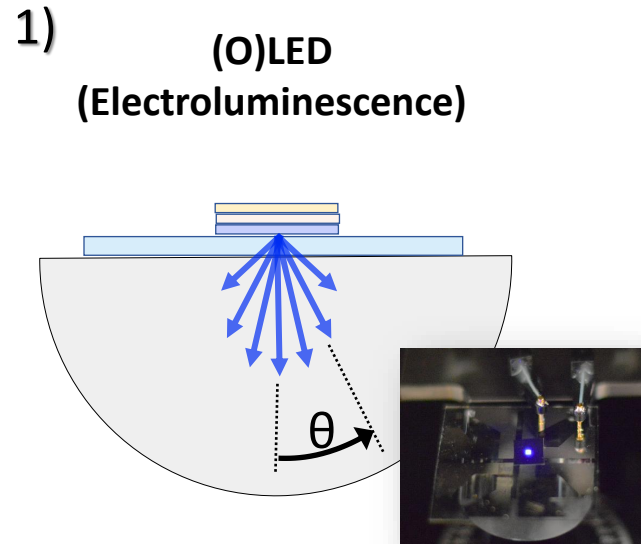


$$EQE = \frac{\text{Photon Flux}}{\text{Electron Flux}}$$

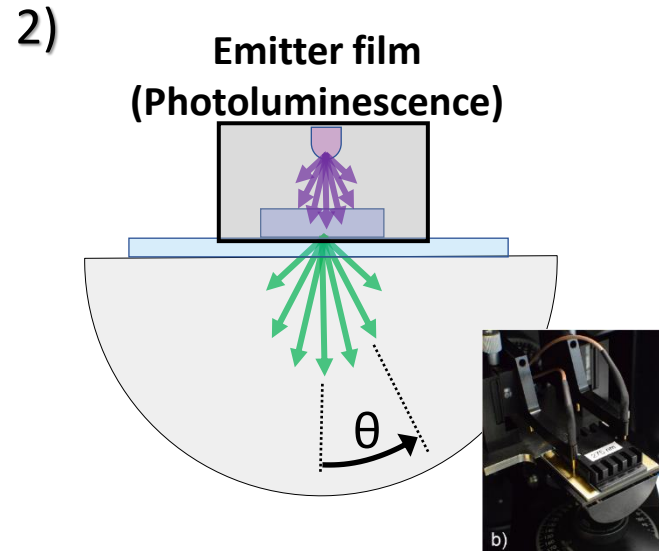
$$\text{Power efficiency} = \frac{\text{Photon Power}}{V \cdot I}$$

$$\text{Luminous efficiency} = \frac{\text{Luminous Flux}}{V \cdot I}$$

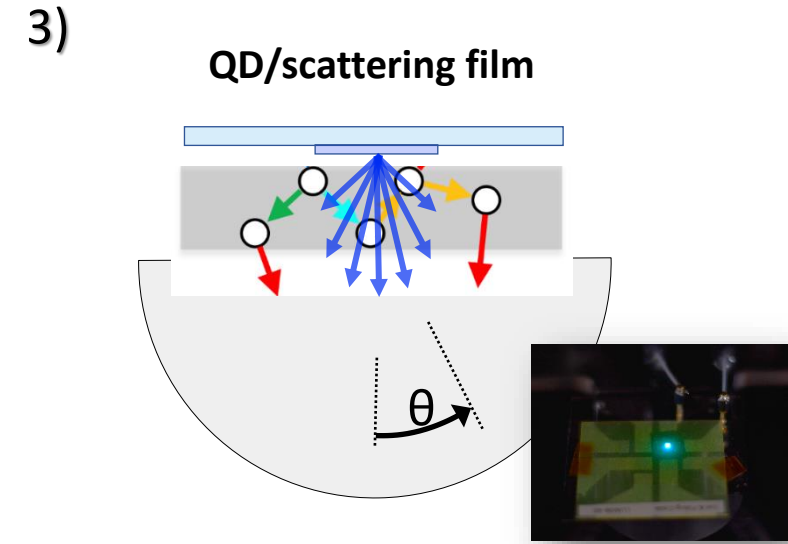
Phelos modes



- Analysis of color
- Efficiency (EQE, lm/W, power eff.)
- Emission zone fit
- Emitter orientation



- Emitter orientation

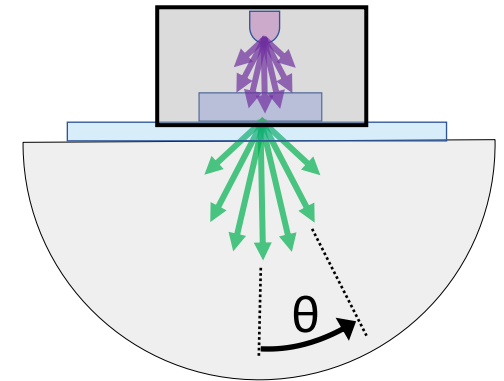
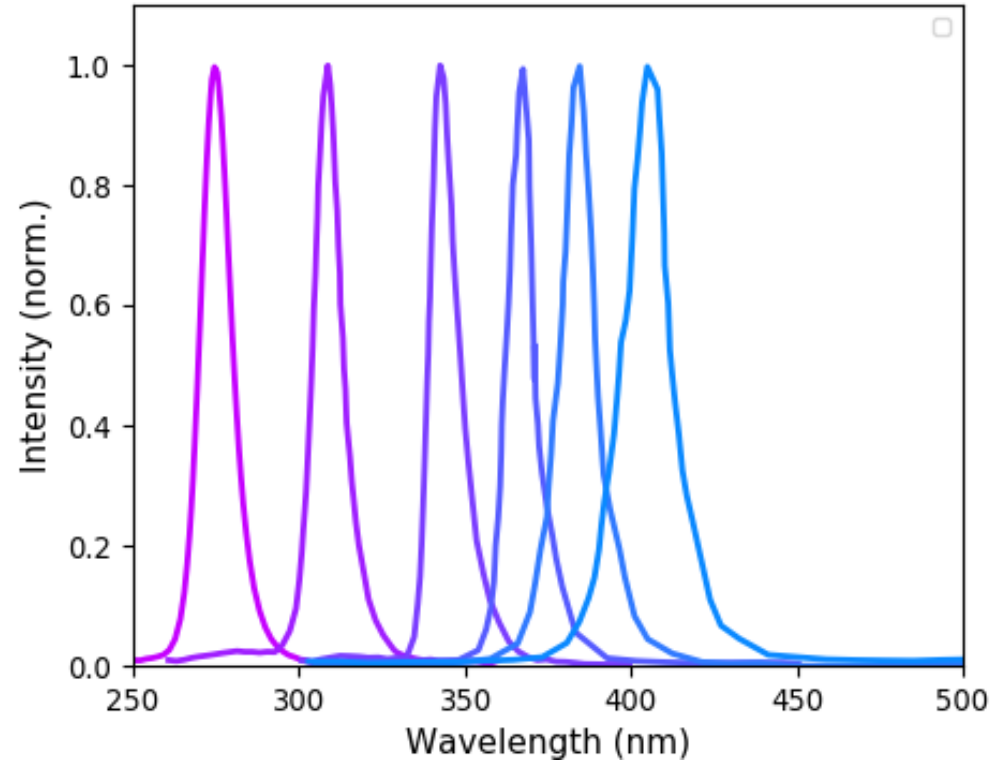


- Scattering/down-conversion film characterization
- OLED with QD characterization

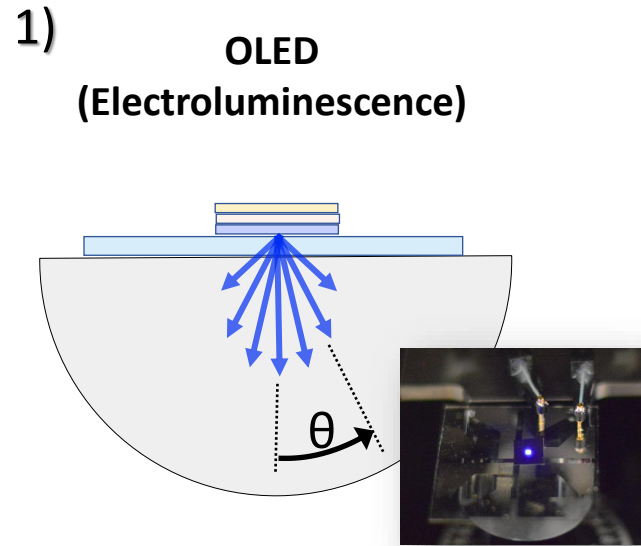
Excitation sources

List of excitation sources

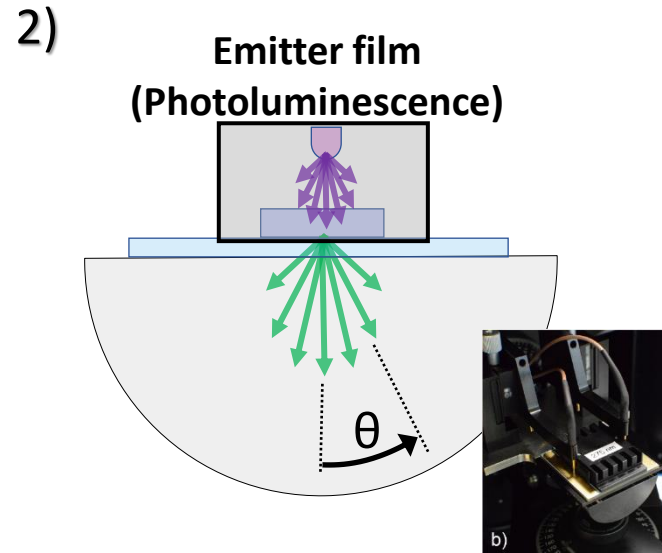
- 275 nm*
- 310 nm*
- 340 nm
- 365 nm
- 385 nm
- 405 nm
- others upon request



Phelos modes

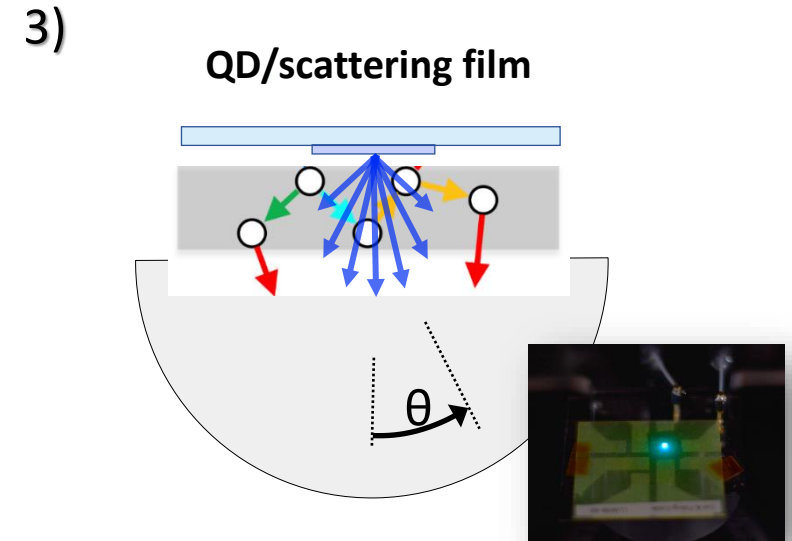
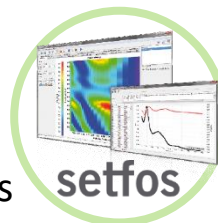


- Analysis of color
- Efficiency (EQE, lm/W, power eff.)
- Emission zone fit*
- Emitter orientation*



- Emitter orientation*

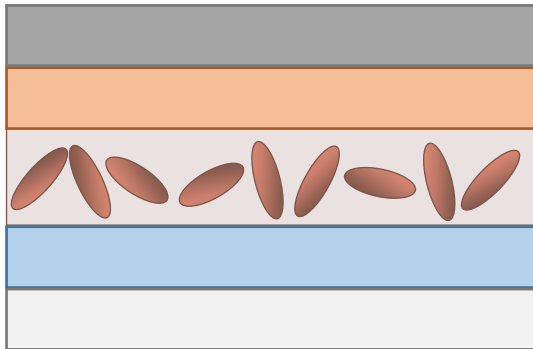
*quantitative analysis requires optical simulations



- Scattering/down-conversion film characterization
- OLED with QD characterization

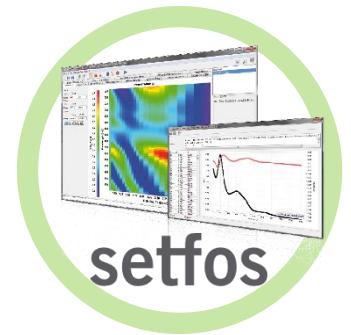
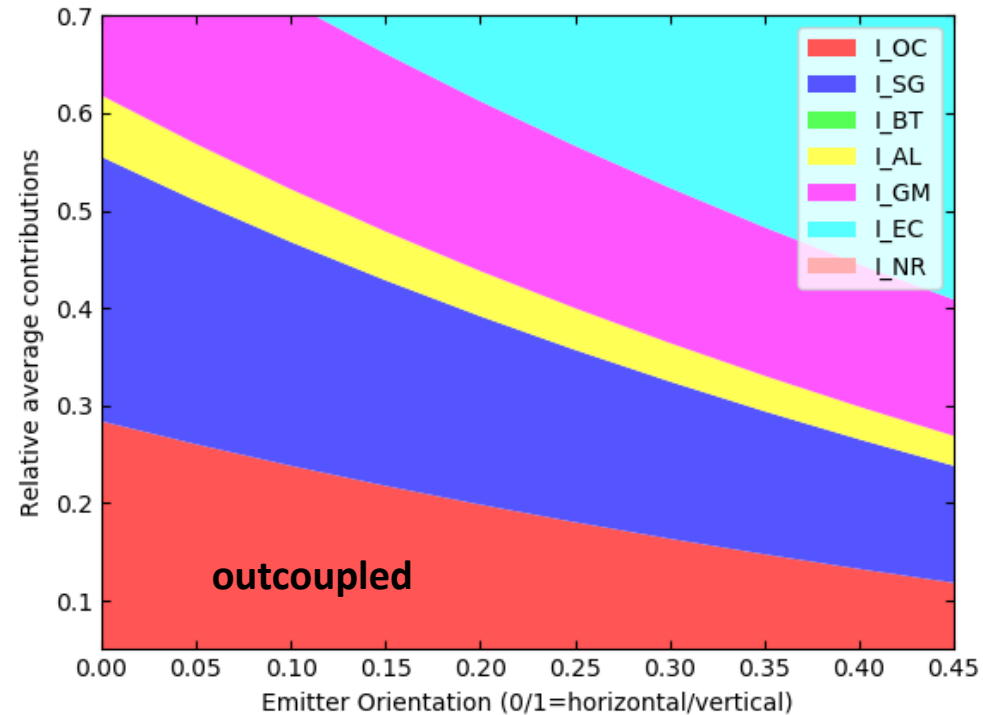
Emitter dipole orientation

Outcoupling efficiency is strongly influenced by the average emitter orientation

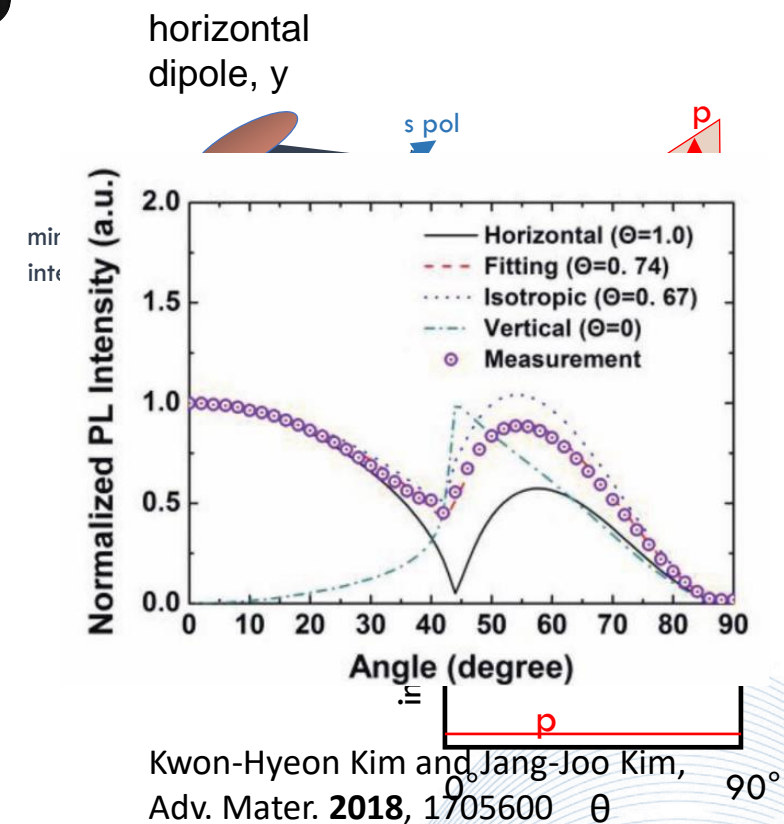
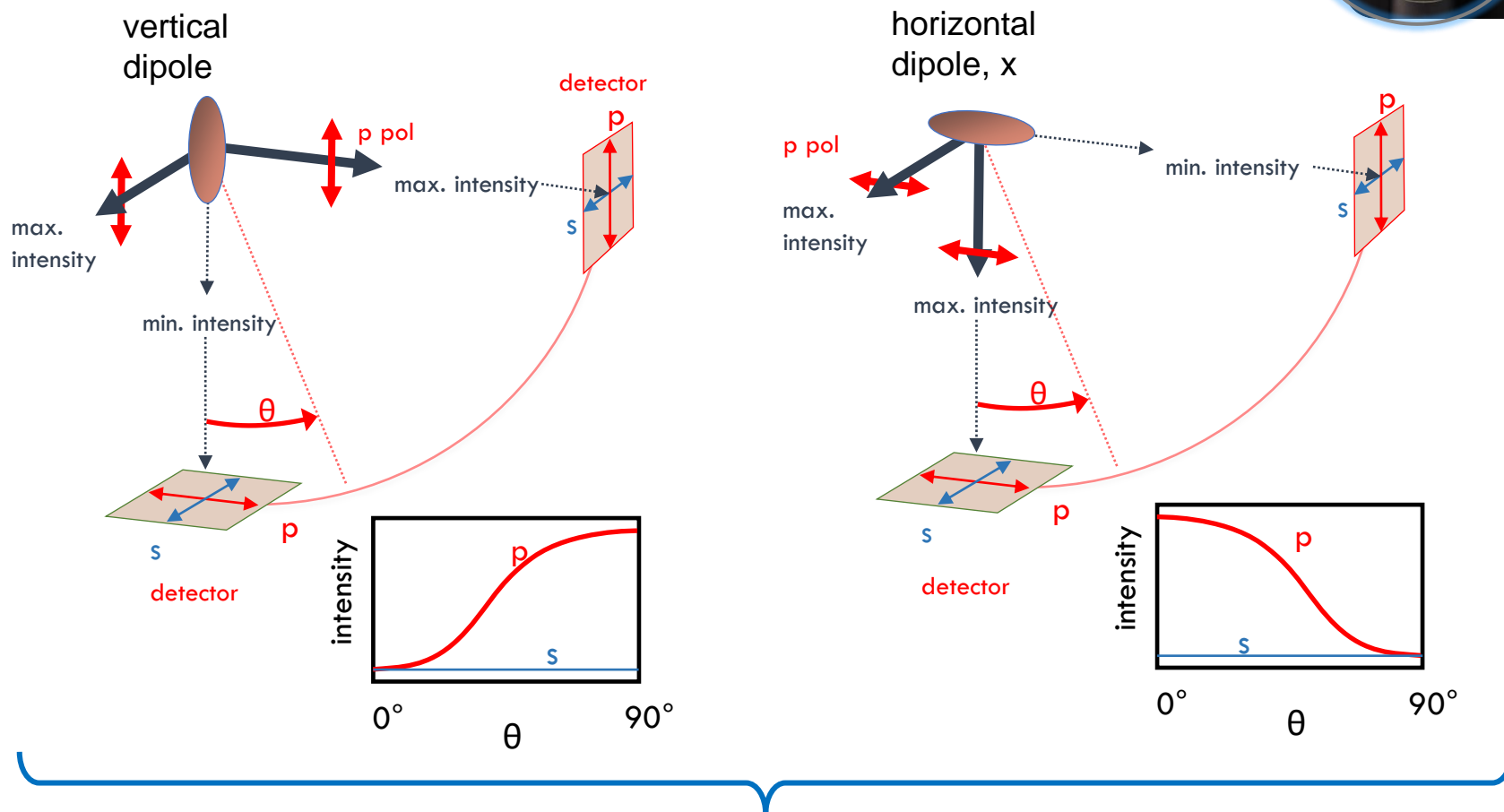
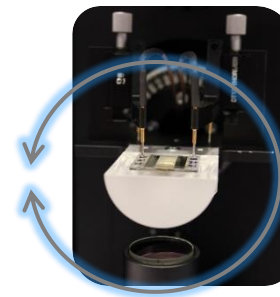


$$EQE = \gamma \cdot \eta_{s,t} \cdot q_{eff} \cdot \eta_{out}$$

Horizontal alignment leads to higher EQE!

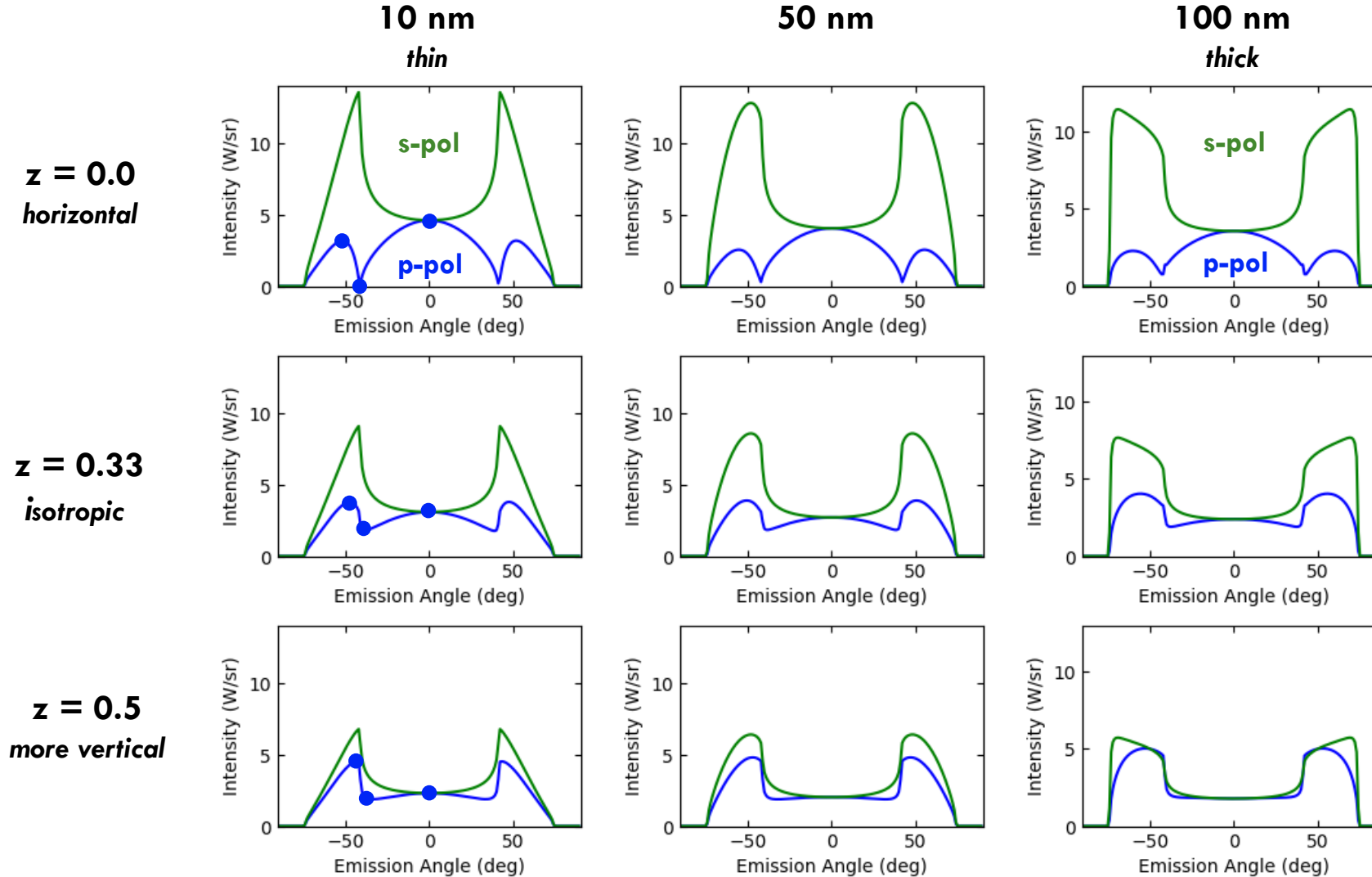


Emitter dipole orientation



-> **p**-polarized emission is sensitive to **emitter orientation**

Angular PL signal: a fingerprint of the dipole orientation

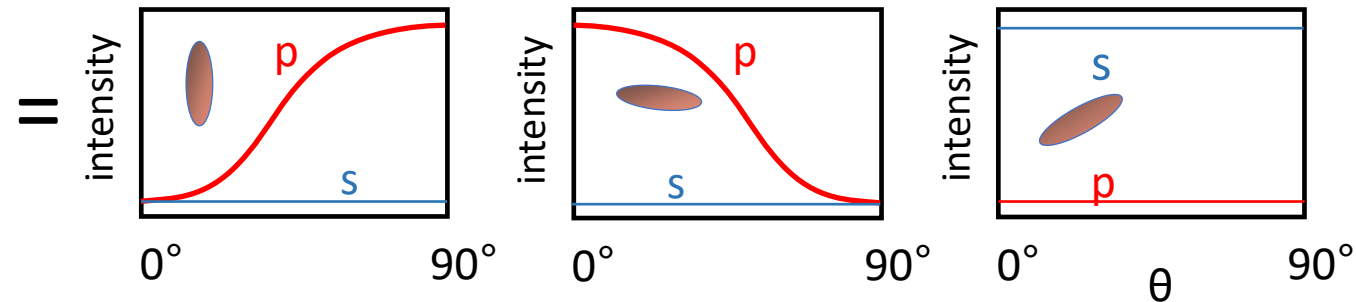


Angular PL signal: a fingerprint of the dipole orientation

Real emitter film:



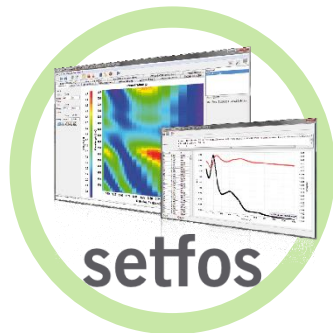
Superposition of statistically distributed dipoles



+ **Further effects:**

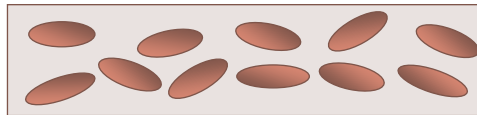
- back-reflection from org-air interface
- interference / cavity effects
- refraction / birefringence

→ accurate description requires full optical modeling



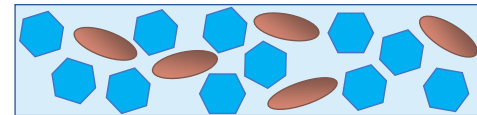
Emitter orientation in host-guest system: example

pure emitter film



- horizontal alignment shown using **VASE** (variable angle spectroscopic ellipsometry)
- order parameter estimated from optical constants / birefringence

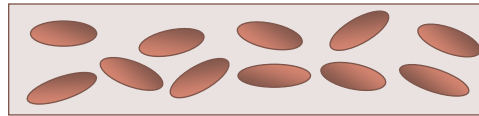
emitter (9%) : host



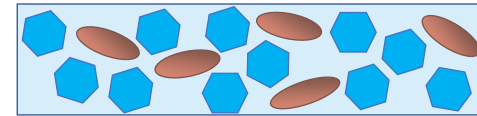
- ellipsometry results reflect optical properties of emitter-host blend
- no information about emitter dipole orientation inside host matrix
- **angular PL** probes emitter orientation directly, independent of host matrix

Emitter orientation in host-guest system: example

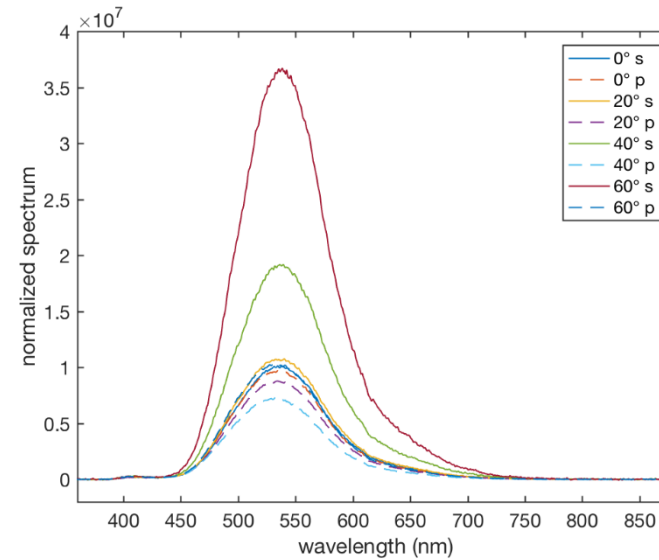
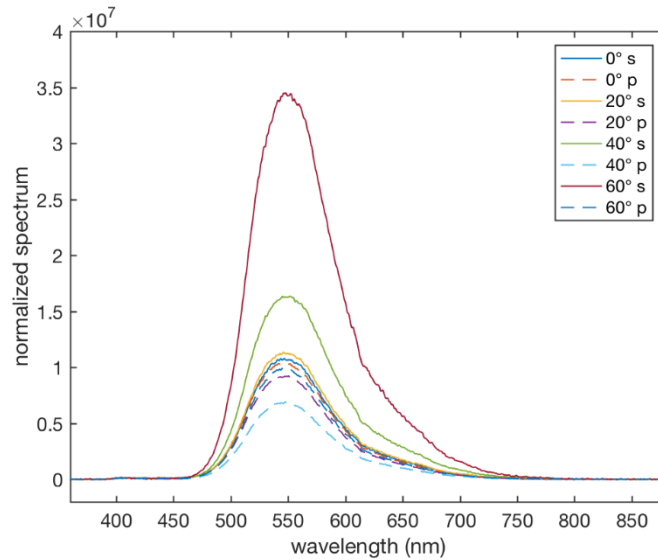
pure emitter film



emitter (9%) : host

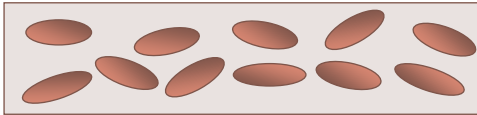


Angular PL, spectral:

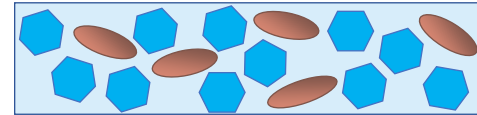


Emitter orientation in host-guest system: example

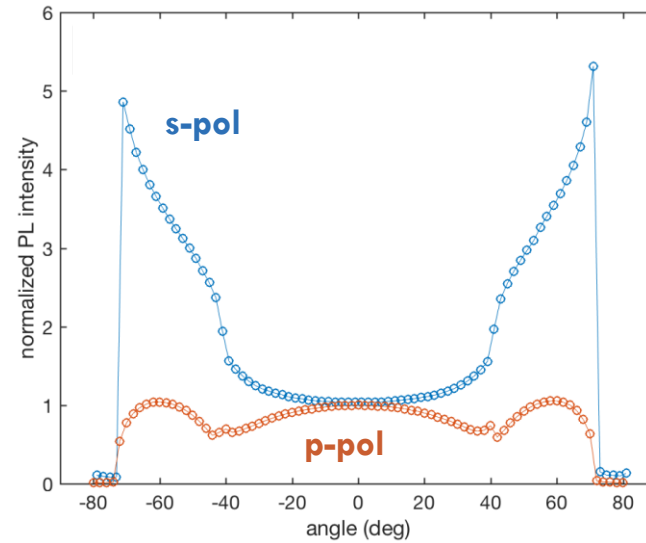
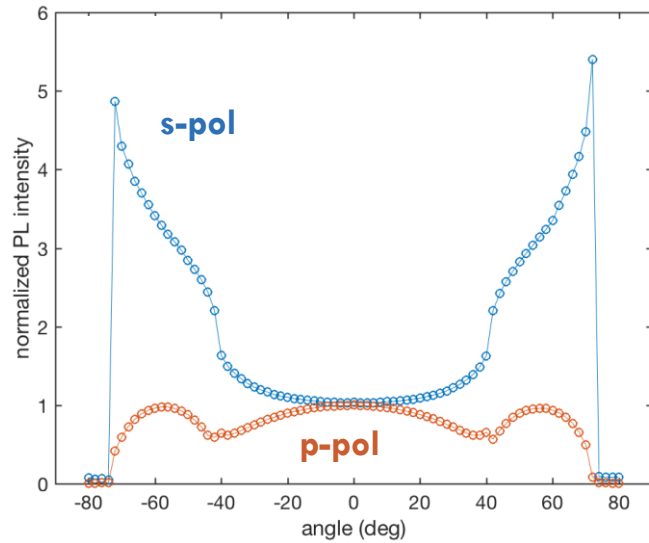
pure emitter film



emitter (9%) : host

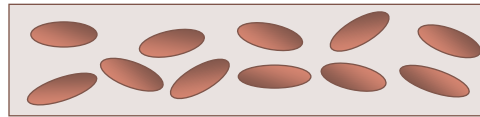


Angular PL, integrated:

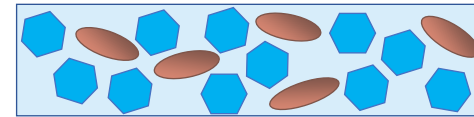


Emitter orientation in host-guest system: example

pure emitter film



emitter (9%) : host



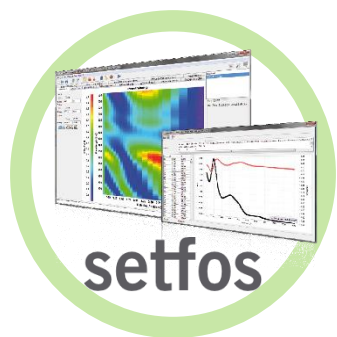
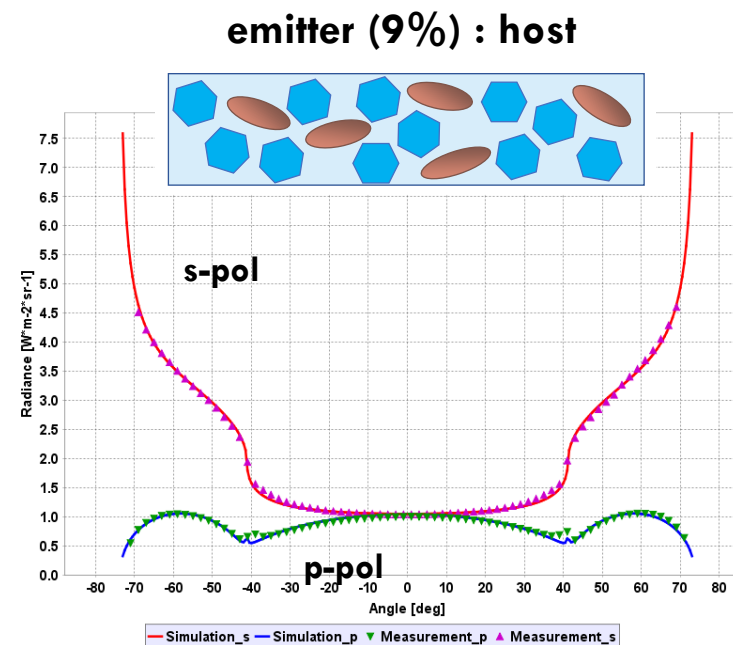
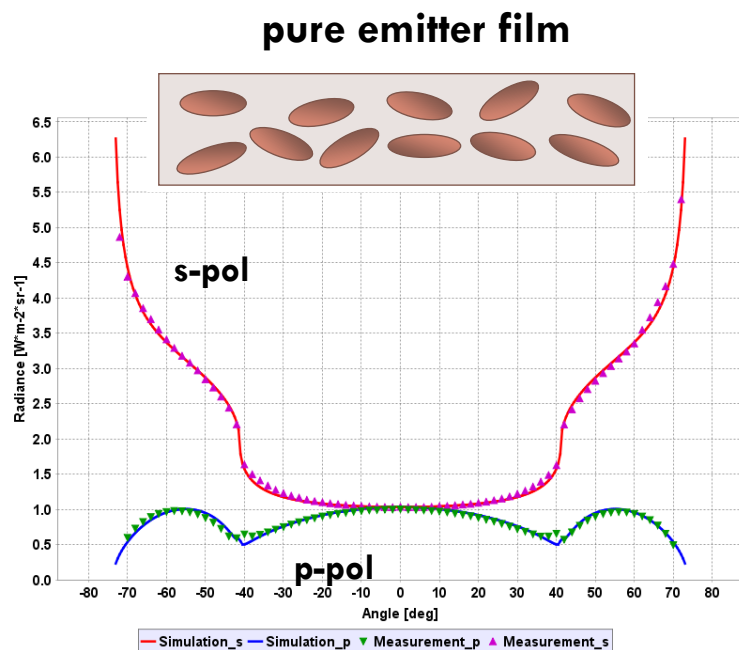
Dipole orientation from model fit

parameters:

- optical constants / birefringence — ellipsometry or fitting parameter of emitter layer and substrate
- film thickness — AFM, crystal-monitor, ellipsometry, fitting parameter
- emitter intensity — scalar fitting parameter
- emitter orientation — **fitting parameter of interest**
- emission zone — e.g. exponential decay (UV absorption)

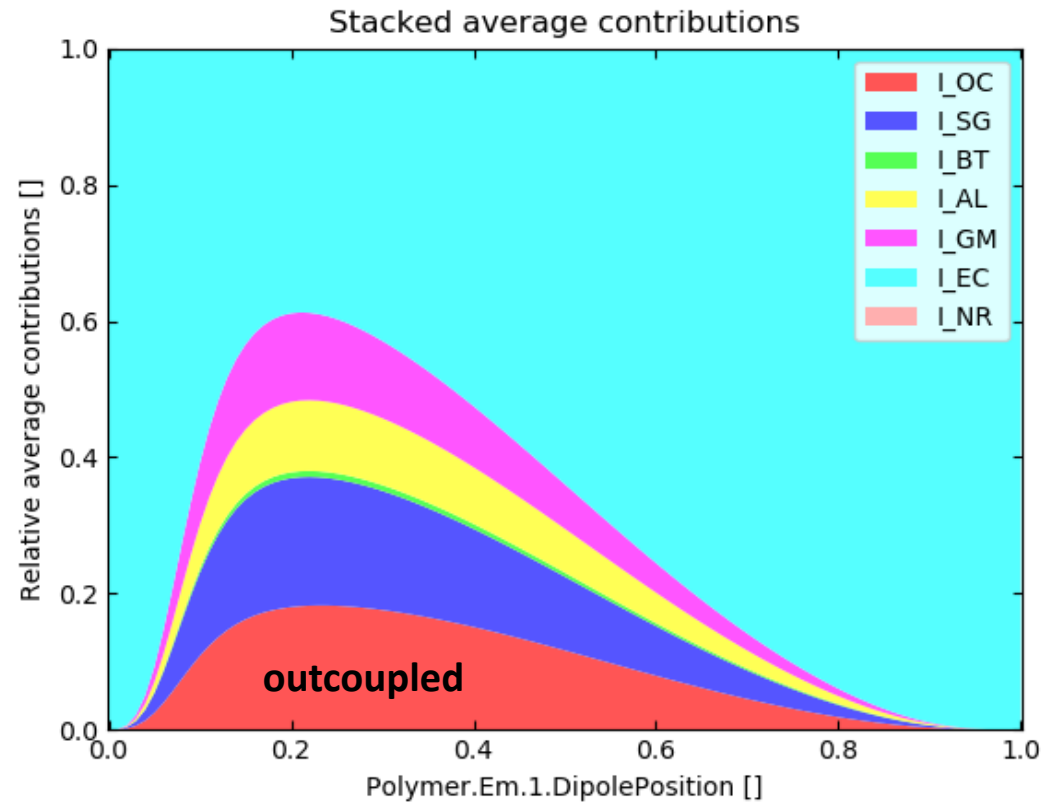
real case study

Emitter orientation in host-guest system: example

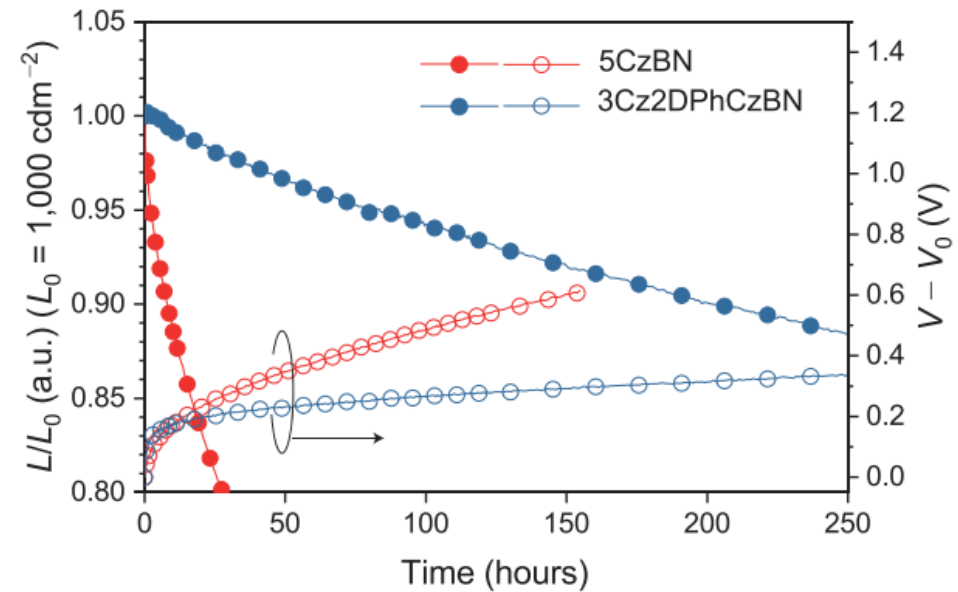


	Pure emitter	Emitter:host blend
nominal thickness (ellipsometry)	53 nm	56 nm
thickness angular PL	53 nm	58 nm
dipole orientation (% vertical)	19.4 %	18.6 %

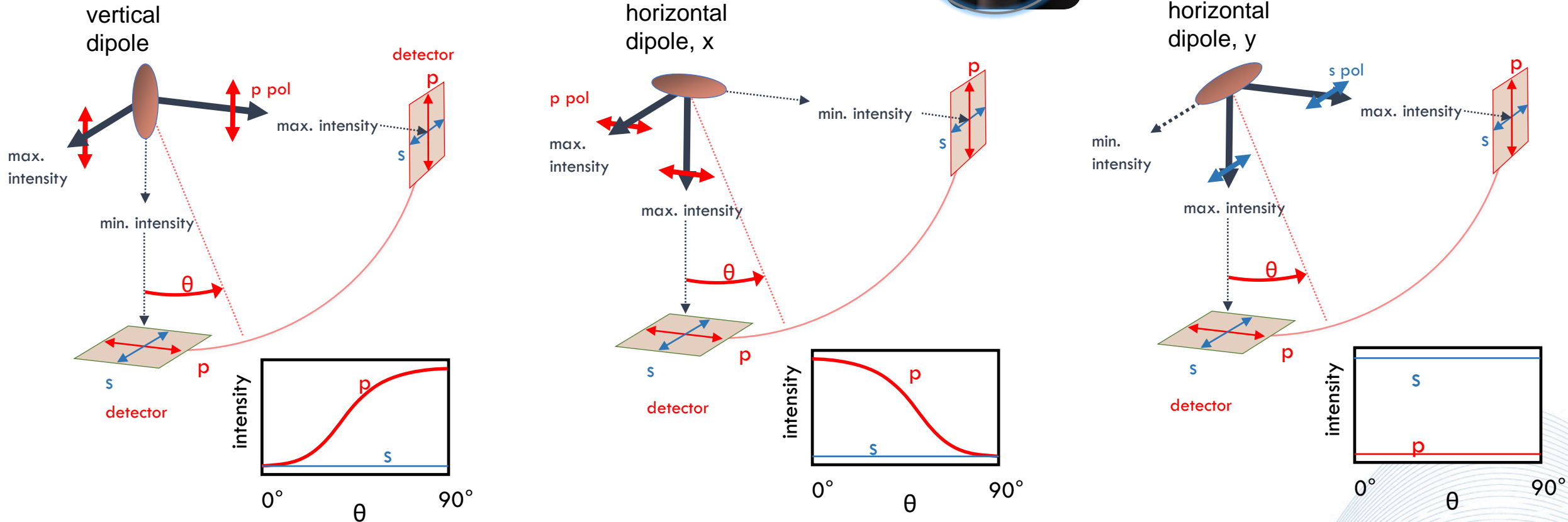
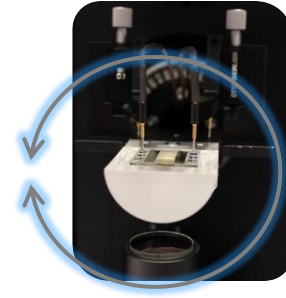
Emitter distribution



- The emitter distribution influences the outcoupling efficiency
- Analyzing the emission zone is necessary to understand degradation



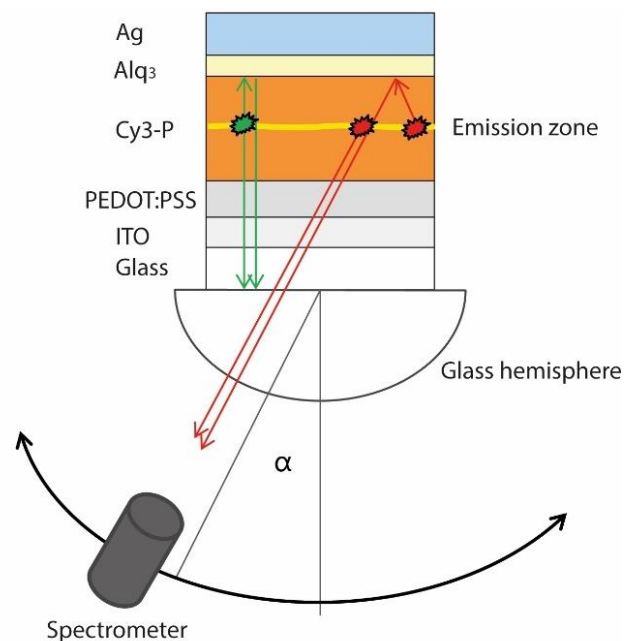
Emitter position determination



Angle-dependent s-polarized emission is independent from the dipole orientation
 -> determination of **emitter distribution**

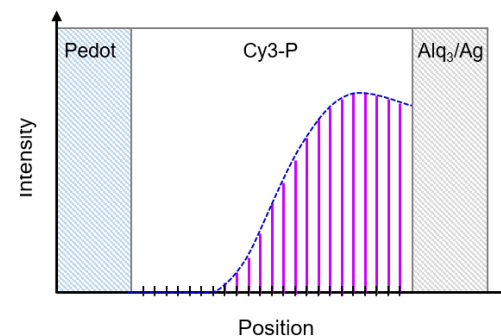
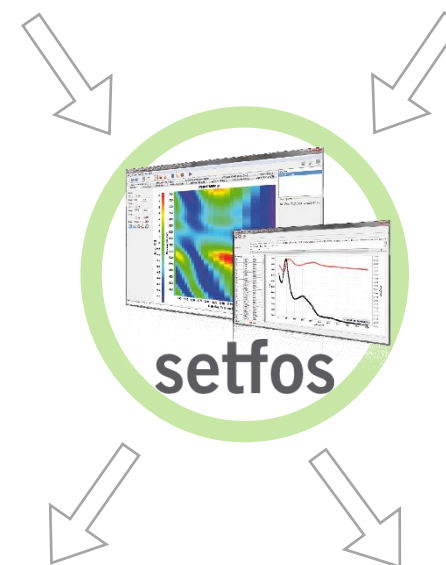
Emitter distribution

- Compare experimental and simulated spectral emission automatically -> emission zone fitting¹
- Use angle dependent data to increase the sensitivity¹



Structure, nk data,
emitter spectrum

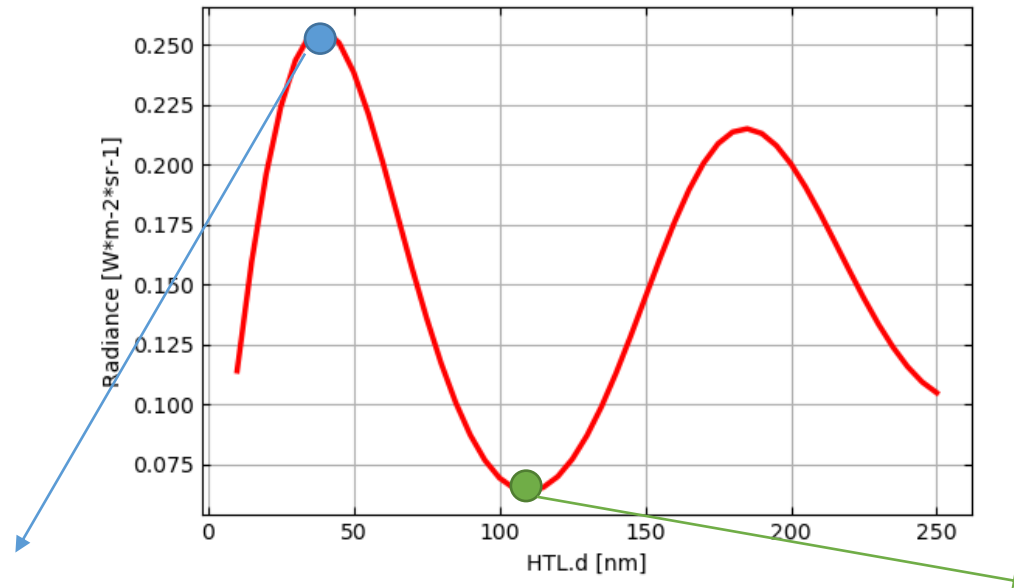
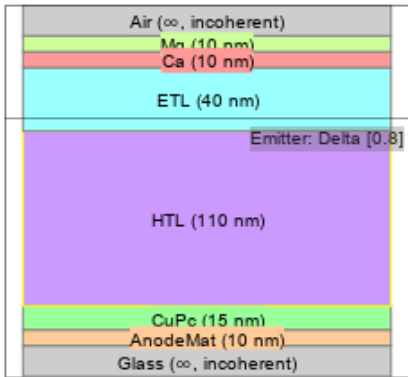
s- (and p-)pol EL
emission spectra



emitter spectrum

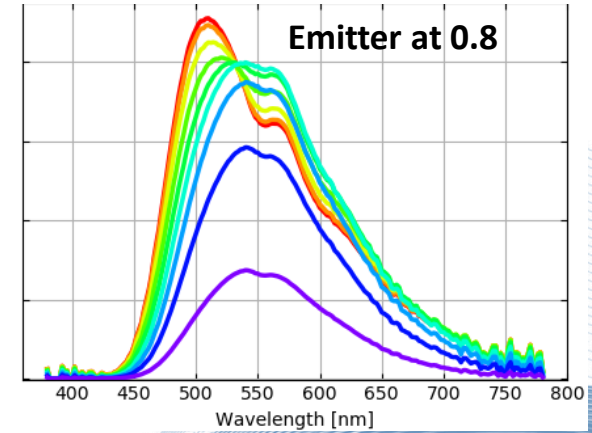
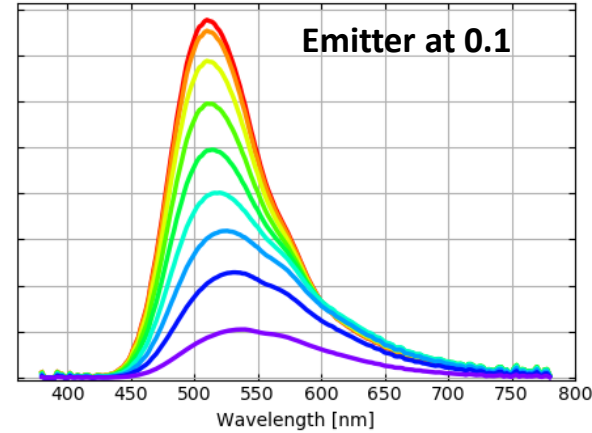
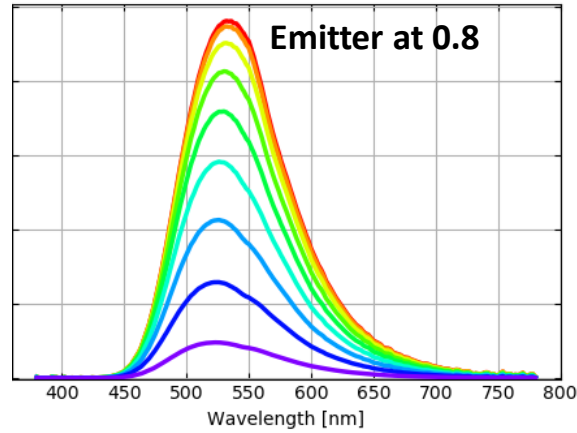
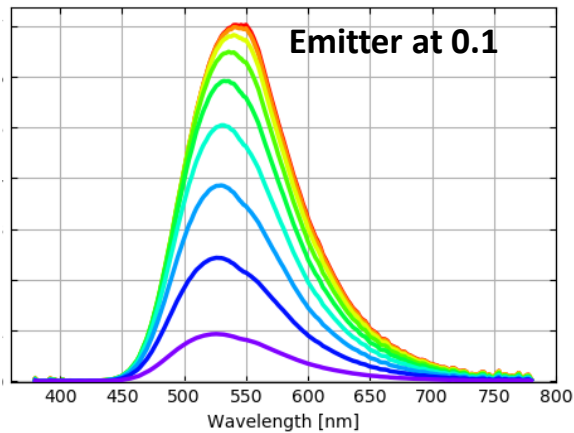
Emitter distribution

Layer structure



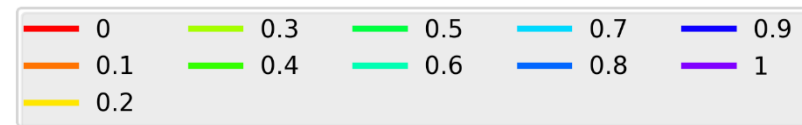
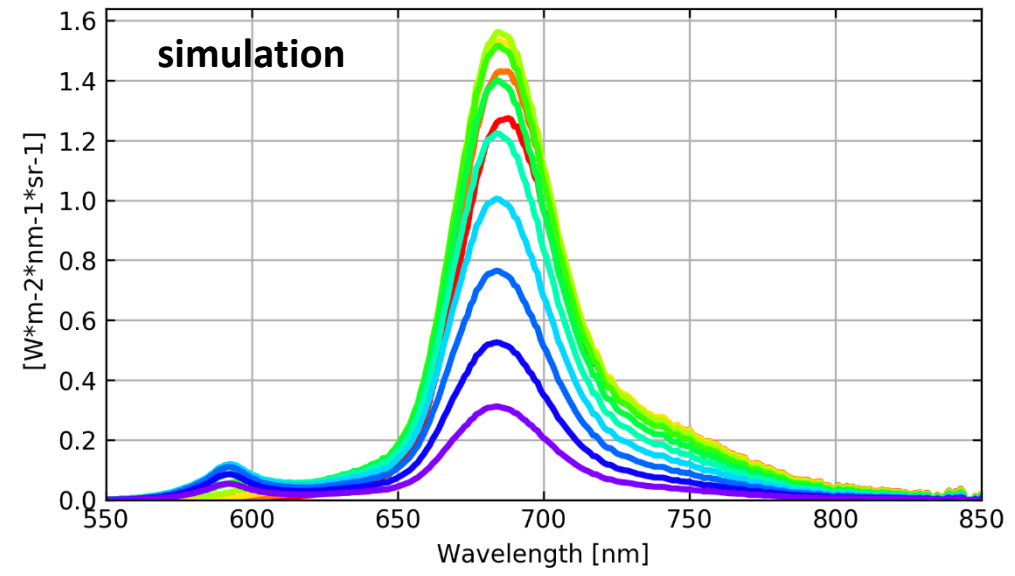
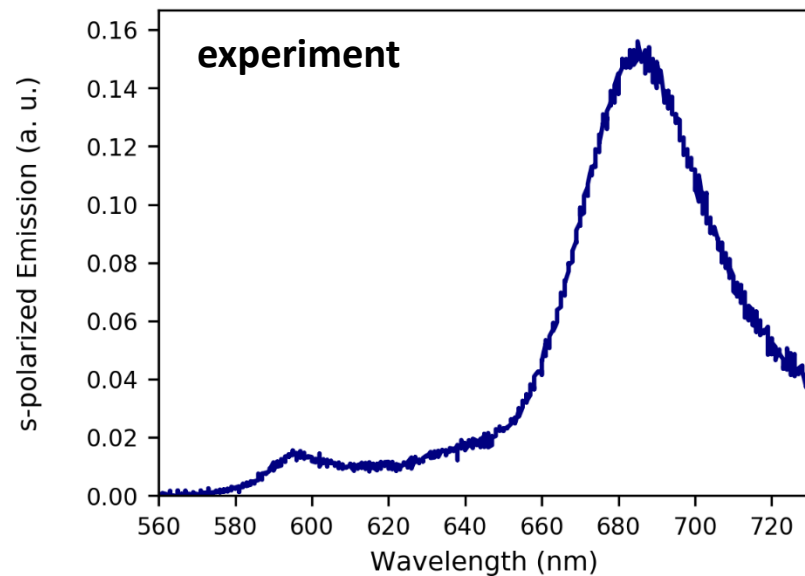
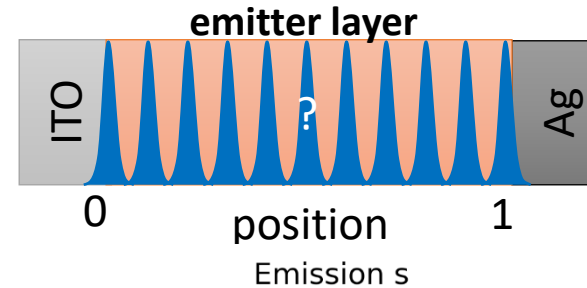
Tuned OLED does not show different spectral emission for different emitter positions

Detuned OLEDs are more suitable for emission zone determination



Emission zone determination: example 1

- Compare experimental and simulated spectral emission
- Use peak ratio to determine position -> **0.67**

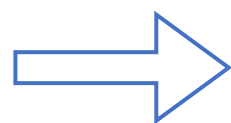
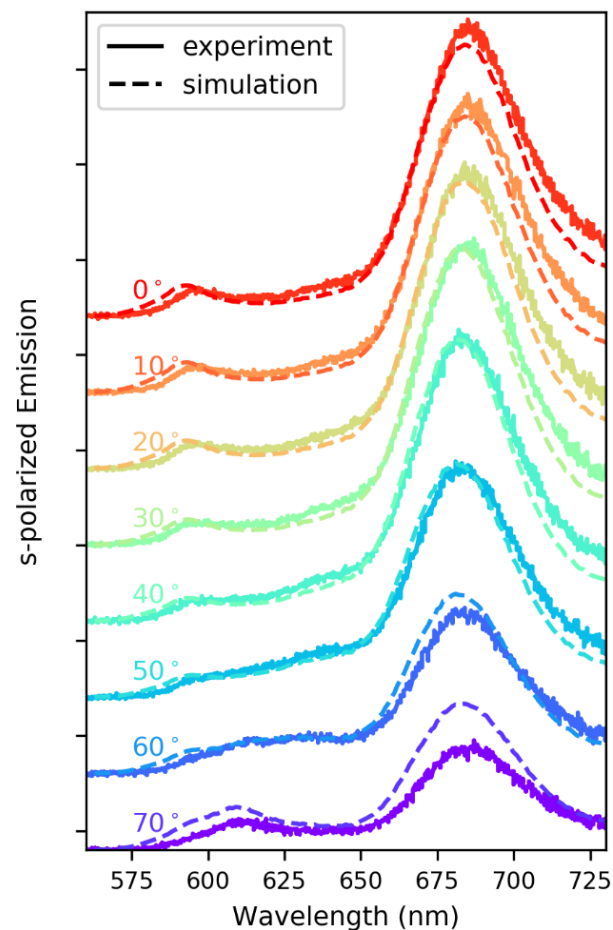


B. Perucco et al., Optics Express **2010**, 18 (S2), A246

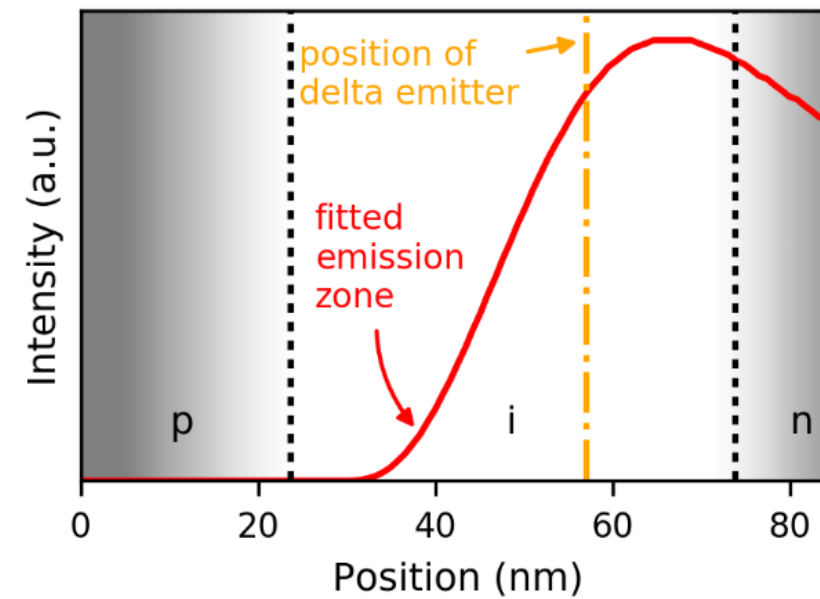
S. Jenatsch et al., ACS Photonics, **2018**, 5 (4), 1591–1598

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Emission zone determination: example 1

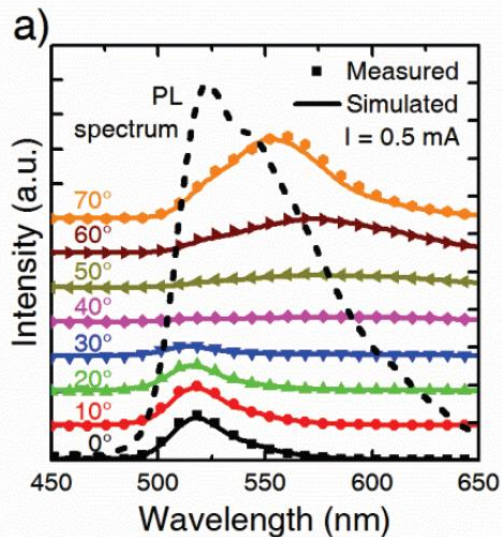
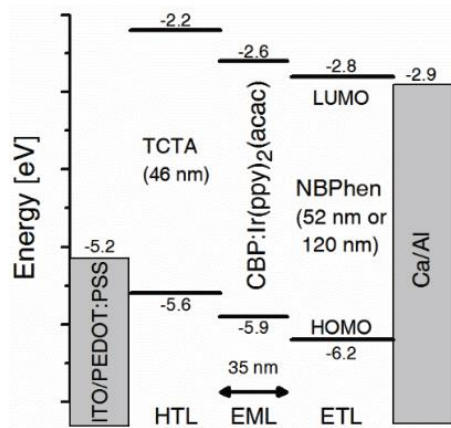


Use full angle dependence to determine the **emitter distribution** inside EML (red line)

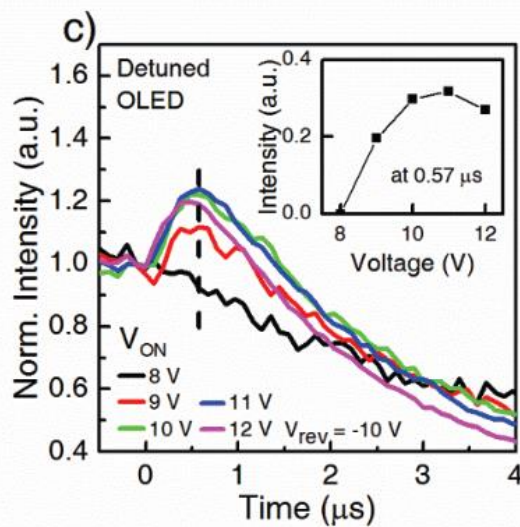
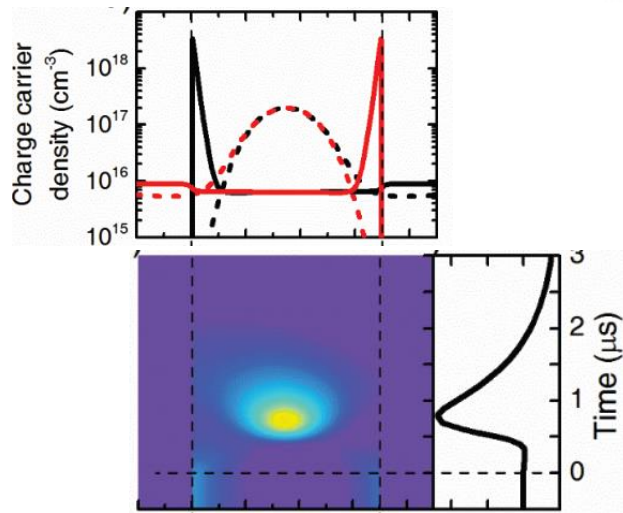
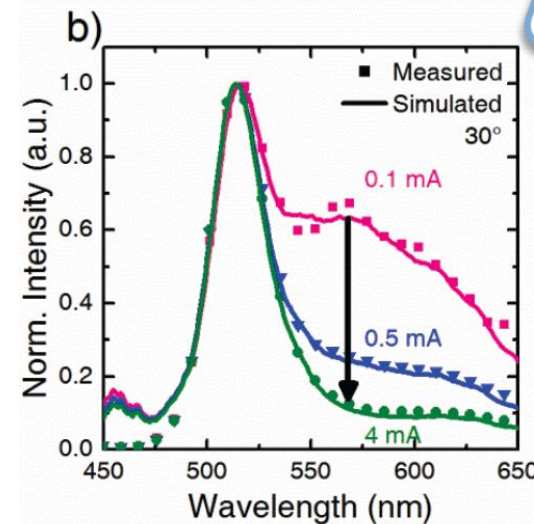


Emission zone determination: example 2

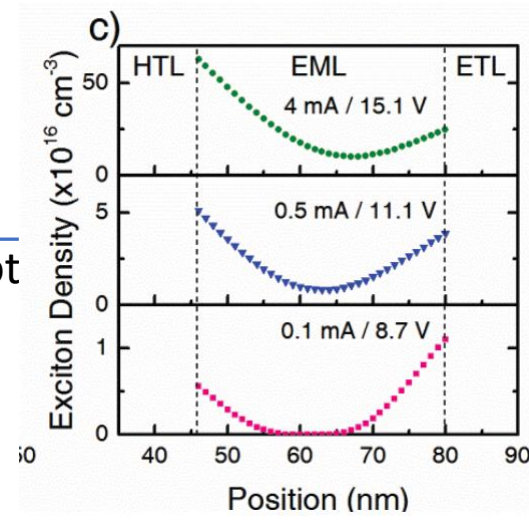
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Bias dependent emission zone

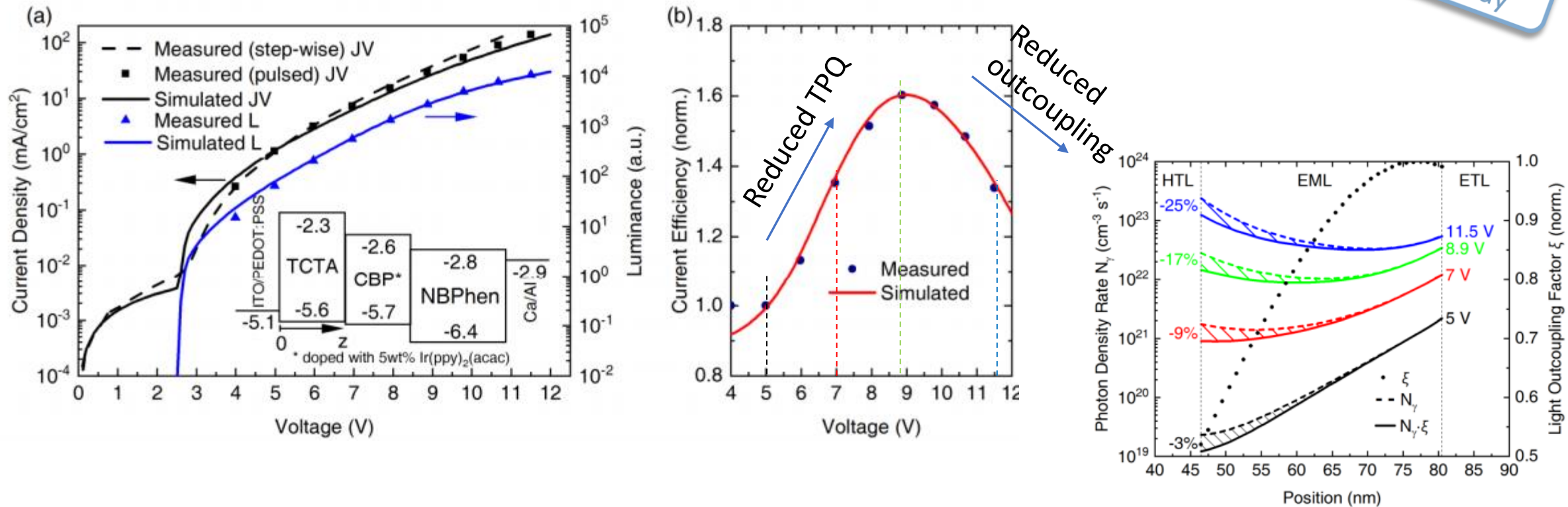


Split emission zone shows TEL overshoot



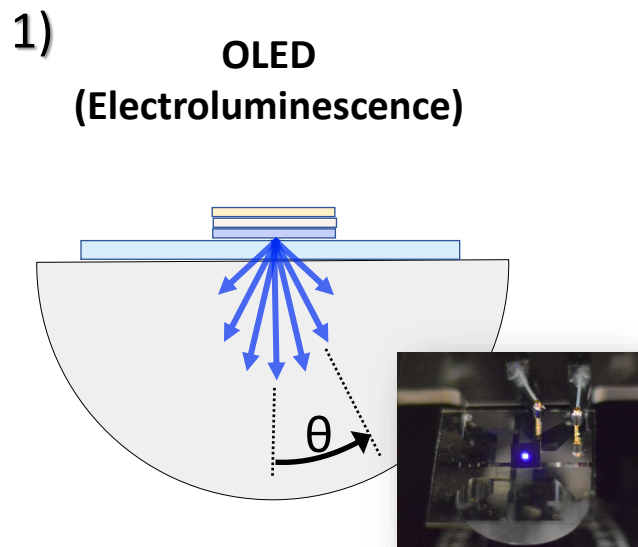
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Emission zone determination: example 2

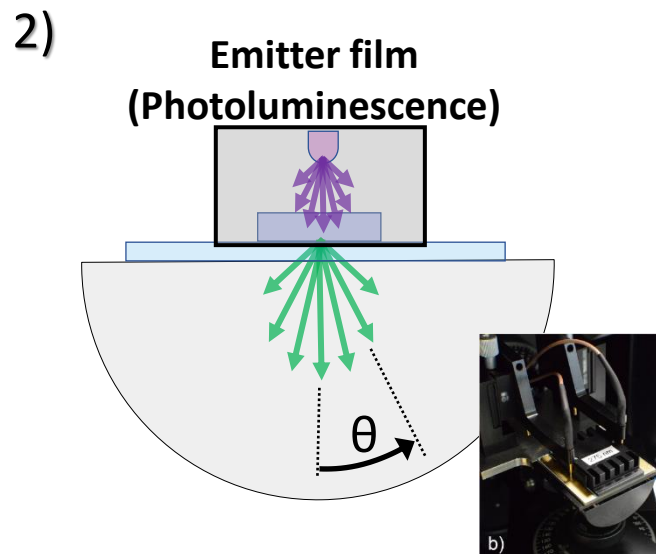


- Reduced outcoupling due to shift of the emission zone results in CE reduction
- Increased TTA contributes to the CE decrease
- Reduced TPQ due to emission zone shifts explains the CE rise

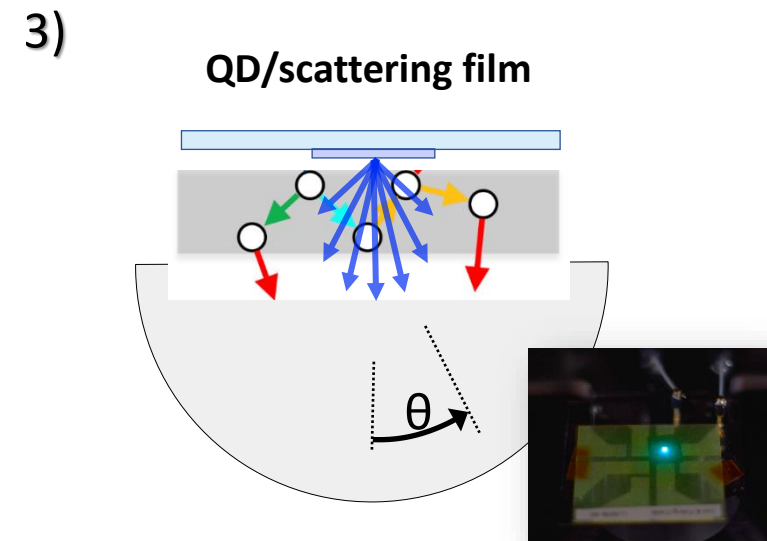
Phelos modes



- Analysis of color
- Efficiency (EQE, lm/W, power eff.)
- Emission zone fit
- Emitter orientation



- Emitter orientation

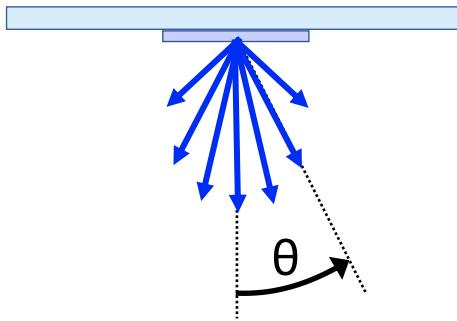


- Scattering/down-conversion film characterization
- OLED with QD characterization

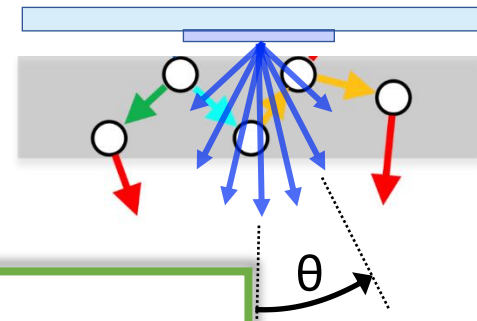
Angular Characterization of QD films

real case study

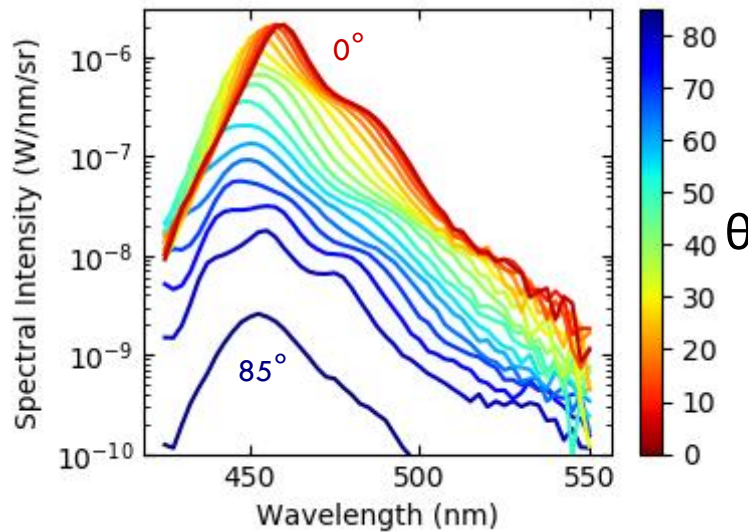
blue TE OLED



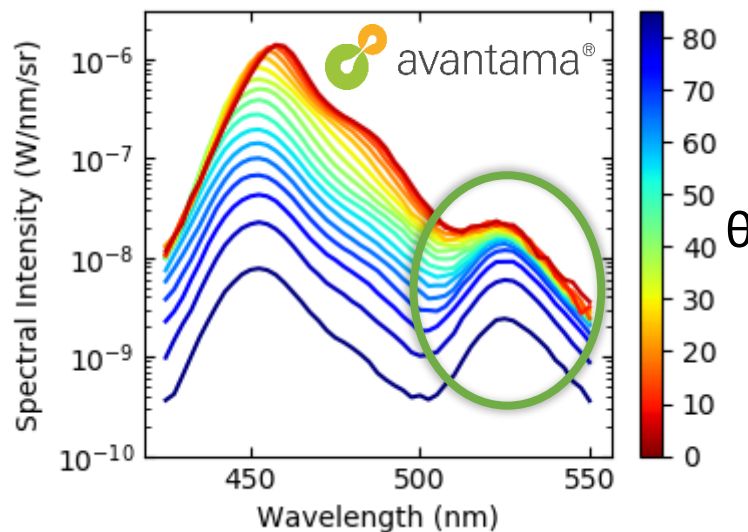
blue OLED + QD film



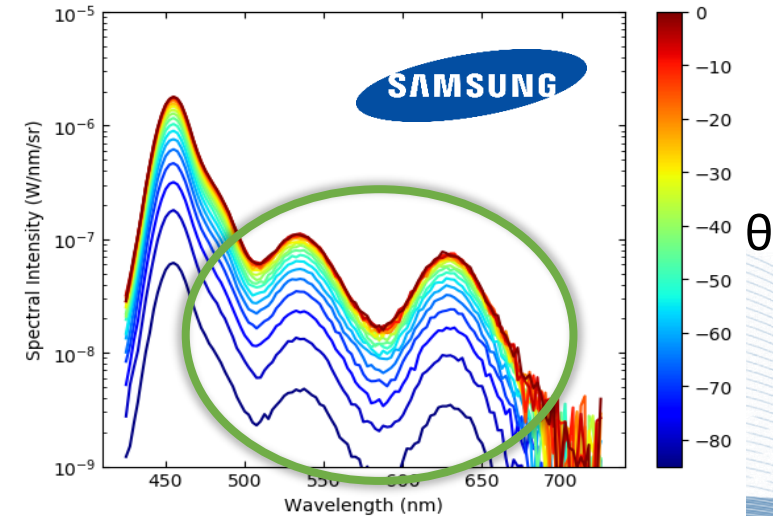
blue OLED



green QD conversion film from Avantama, Switzerland



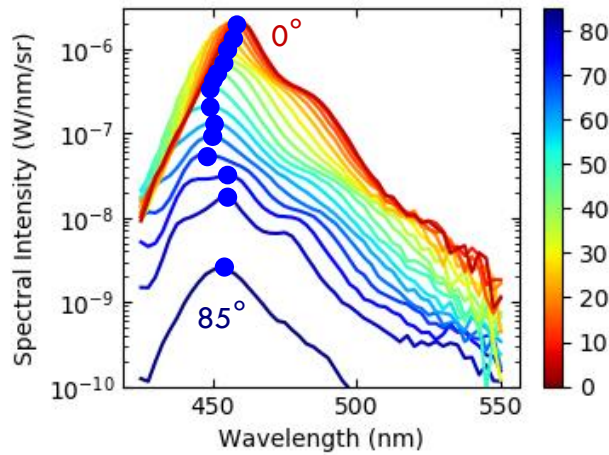
green+red QD conversion film from Samsung QD TV



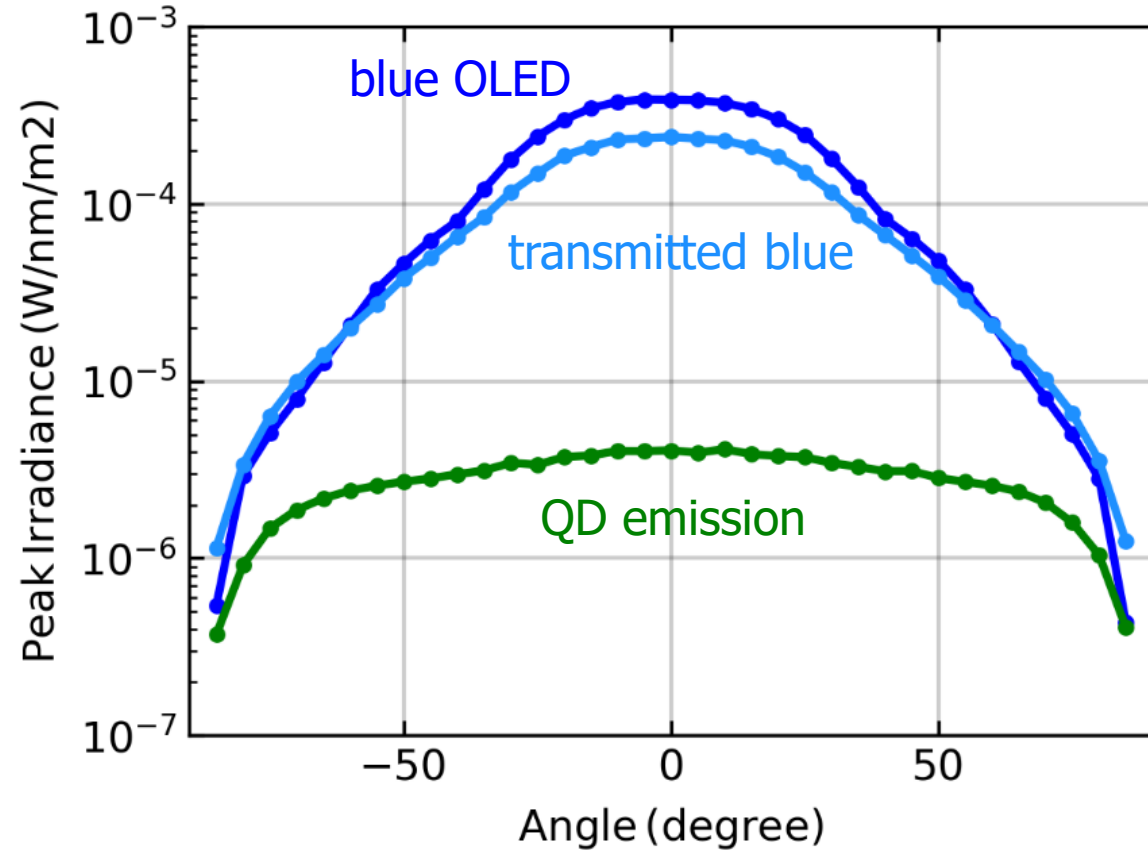
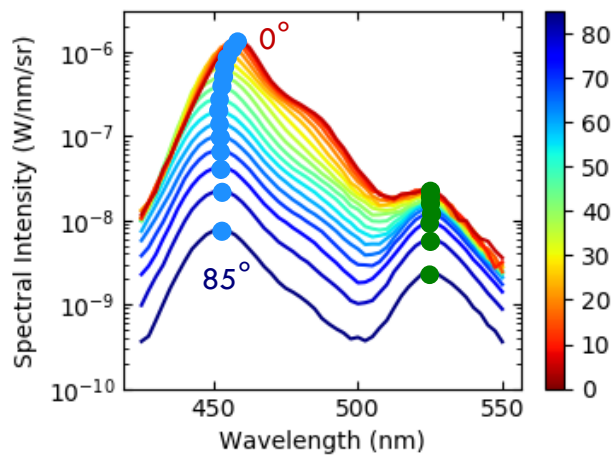
Green emitting perovskite down conversion film

real case study

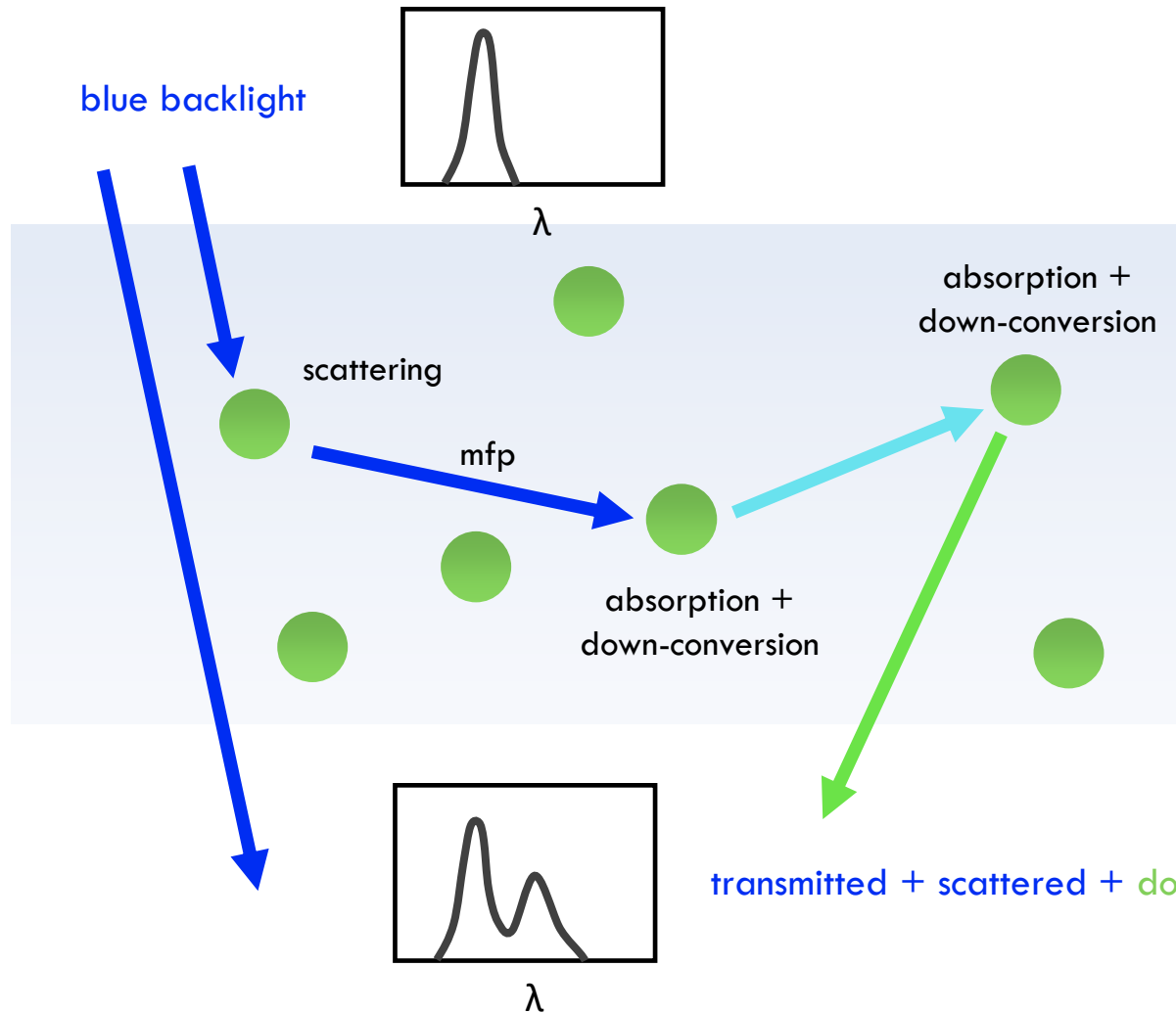
blue OLED



QD film



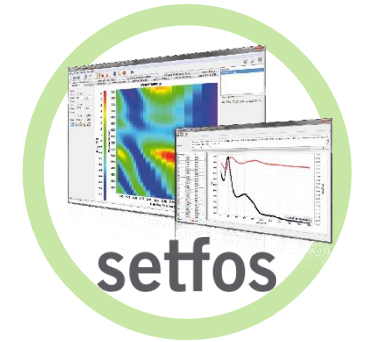
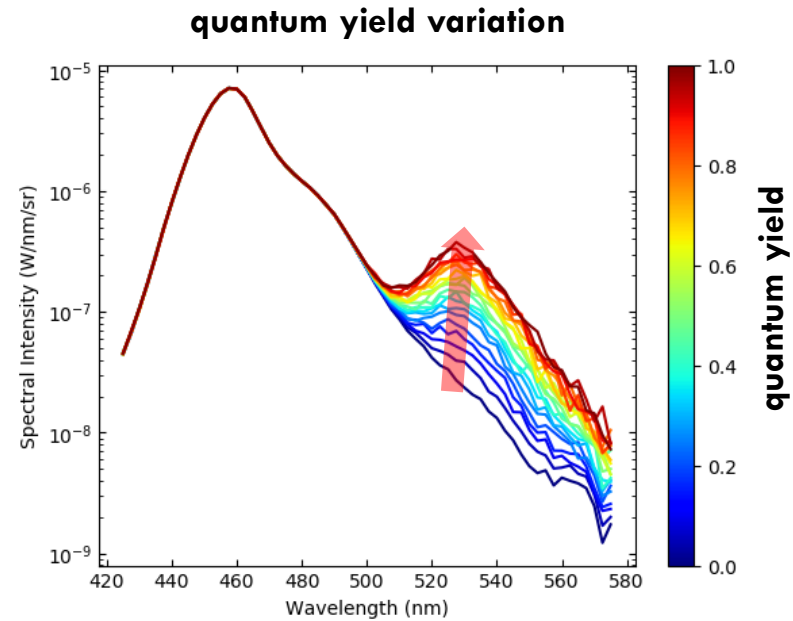
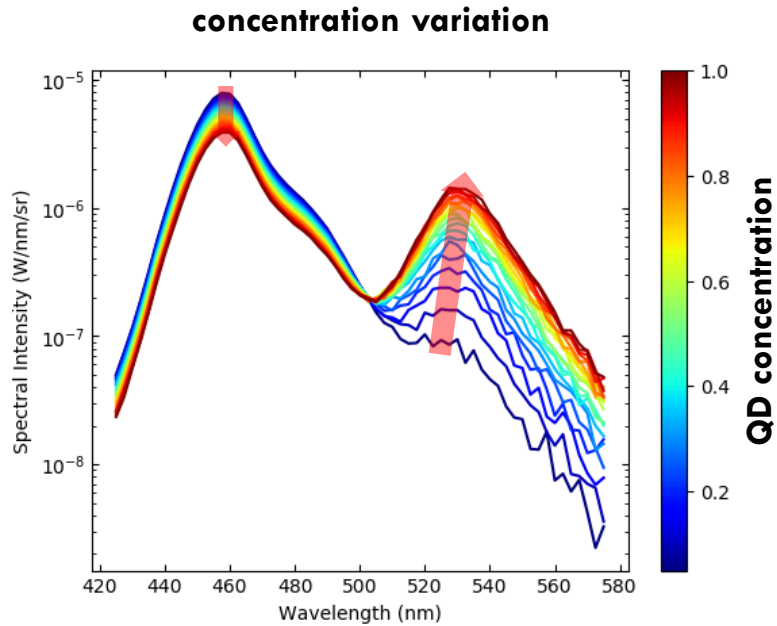
Modeling the QD downconversion: Setfos 4.6



Model parameters:

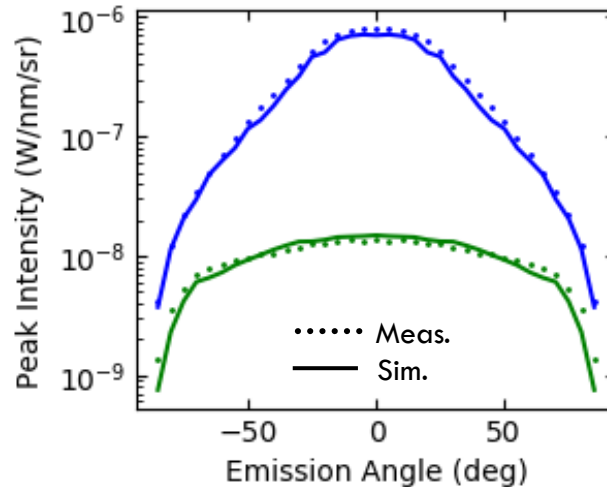
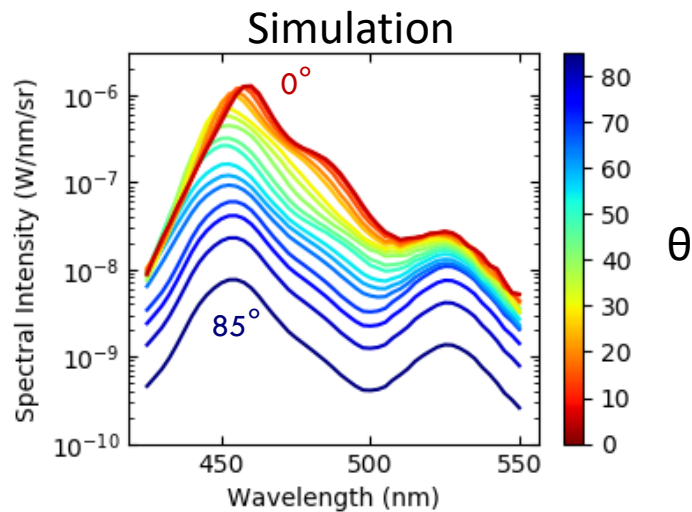
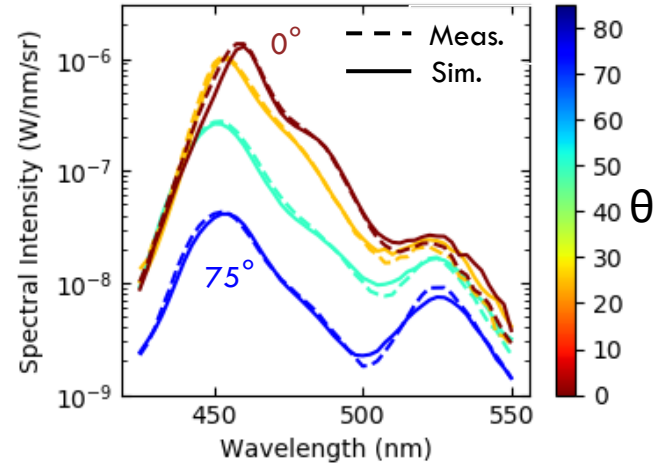
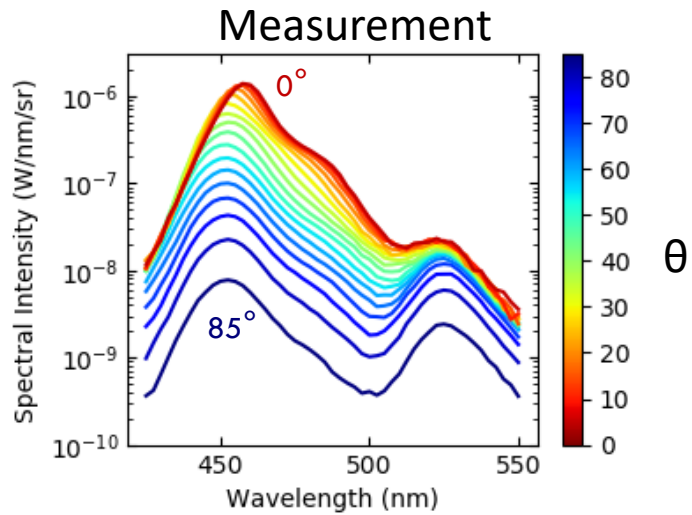
- QD radius
 - concentration
 - refractive index
- scattering cross section
→ mean-free-path
- QD absorption spectrum
 - QD emission spectrum
 - quantum yield

QD downconversion simulation: examples



Fitting results

real case study



Model parameters:

- Mean-free path:
 $mfp = 0.02 \times mfp_{\text{solution}}(\lambda)$
 \Leftrightarrow concentration: 0.6 wt%
- Quantum yield:
 $QY = 99\%$
- QD absorption probability
 $\alpha = 6\% @450\text{nm}$
 $\rightarrow 94\%$ of the blue light is scattered
 $\alpha < 1\% @525\text{nm}$
 \rightarrow green light not re-absorbed